

Optical and Infrared Detectors

Tim Hardy

Outline

- Introduction
- History
- Charge Coupled Devices (CCDs)
 - Break
- CMOS imagers
- Hybrid CMOS imagers
- Other

Introduction

- Who am I?
- Why are detectors important?
- What is a detector?
- What information can we get?
- What causes imprecision?

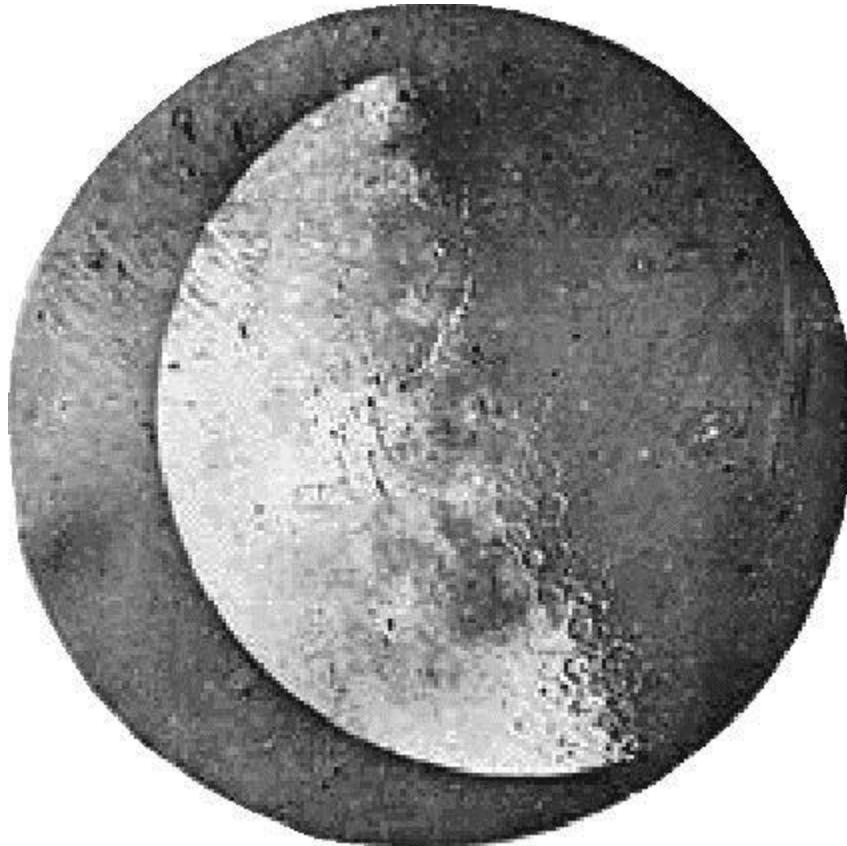
History



History

Il 13.7.1900
Giore si vide ucc. * occ.
Ali 8 ucc. * * * * * * * *
Il \oplus era diritto et ad retrogrado
Ali 12. si addo. in tale direzione * * * *
Il 13. si vide minore in Giore & Stelle * * * * singolarissimi
Ali 14. singolare * * * *
Il 15. * * * * la prof. e' di minore la forma di-
stante della gr. 1 appena finita
Le spese delle 3 autoradi si son
maggior del doppio di q. et con
una in linea retta.

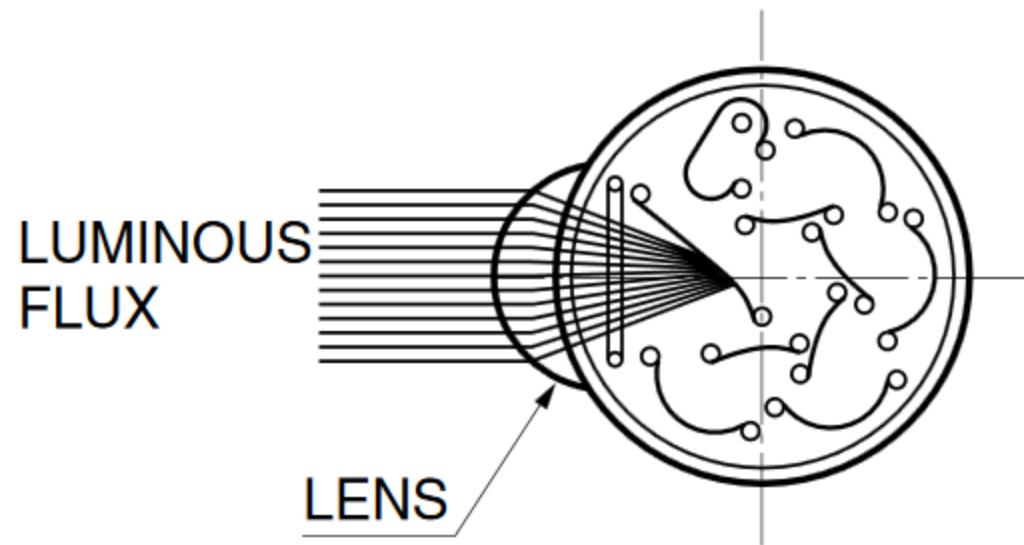
History



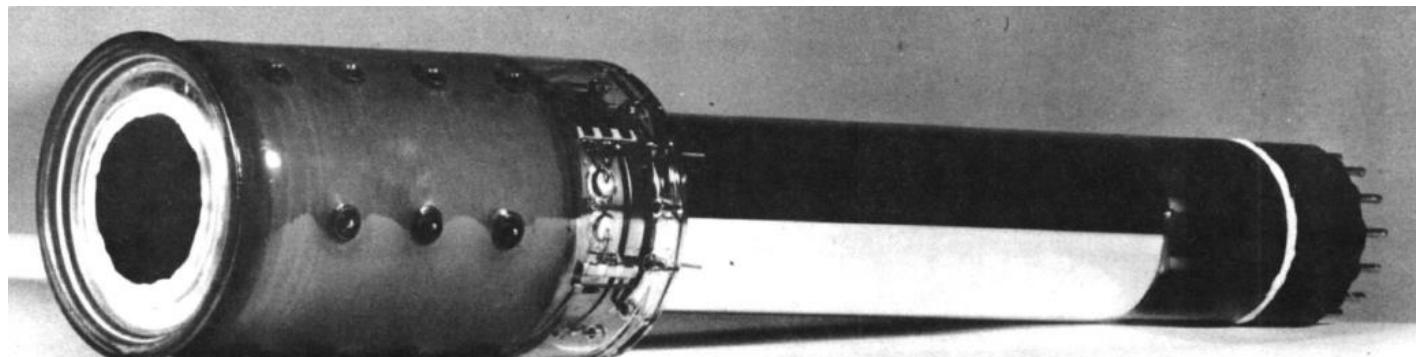
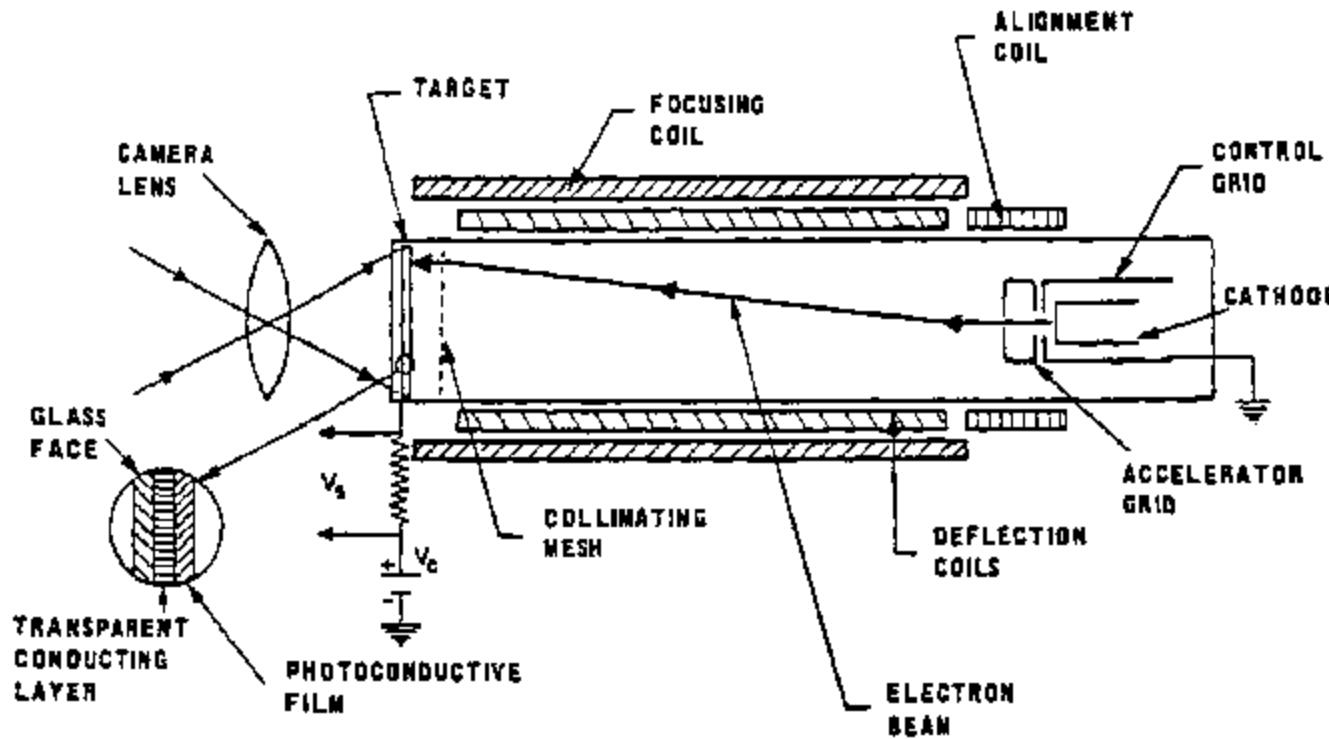
Daguerreotype of the Moon taken by John William Draper in 1845.
Source: New York University Archives

Electronic detectors

- PMT (photoelectric effect)

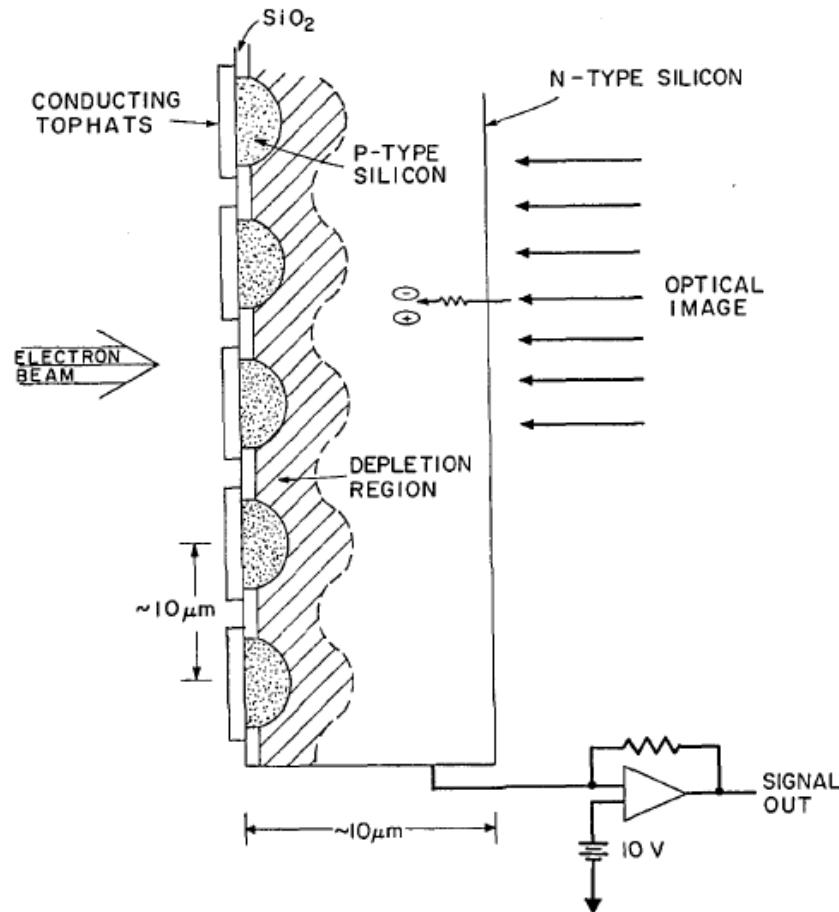


Electronic detectors



Vidicon tube (Zucchino and Lowrance 1971)

Electronic detectors



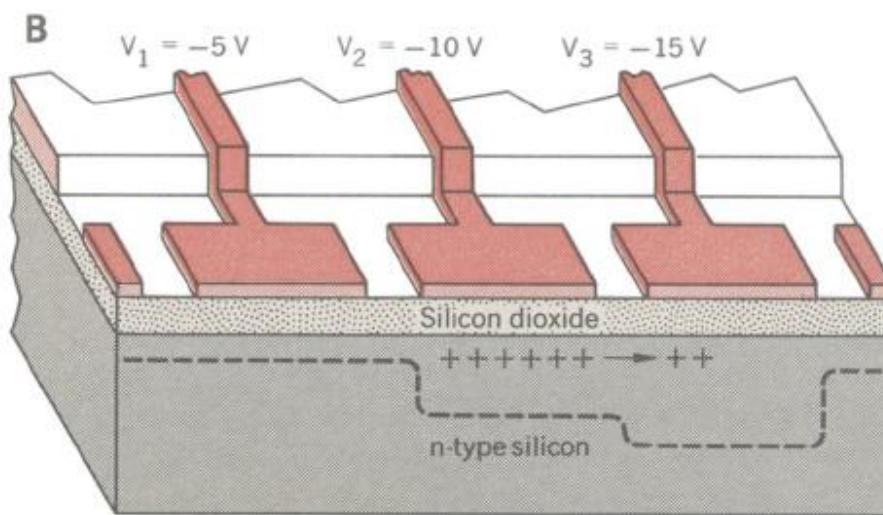
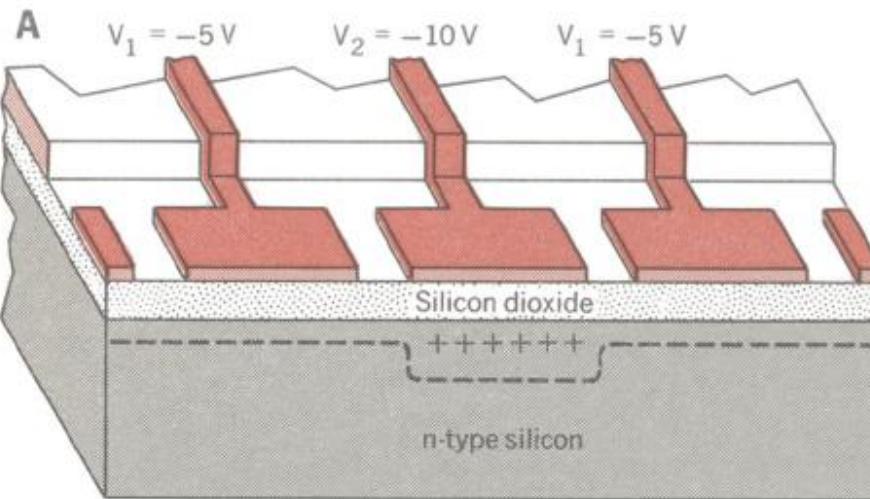
Silicon photodiode vidicon target (McCord & Westphal, 1972)

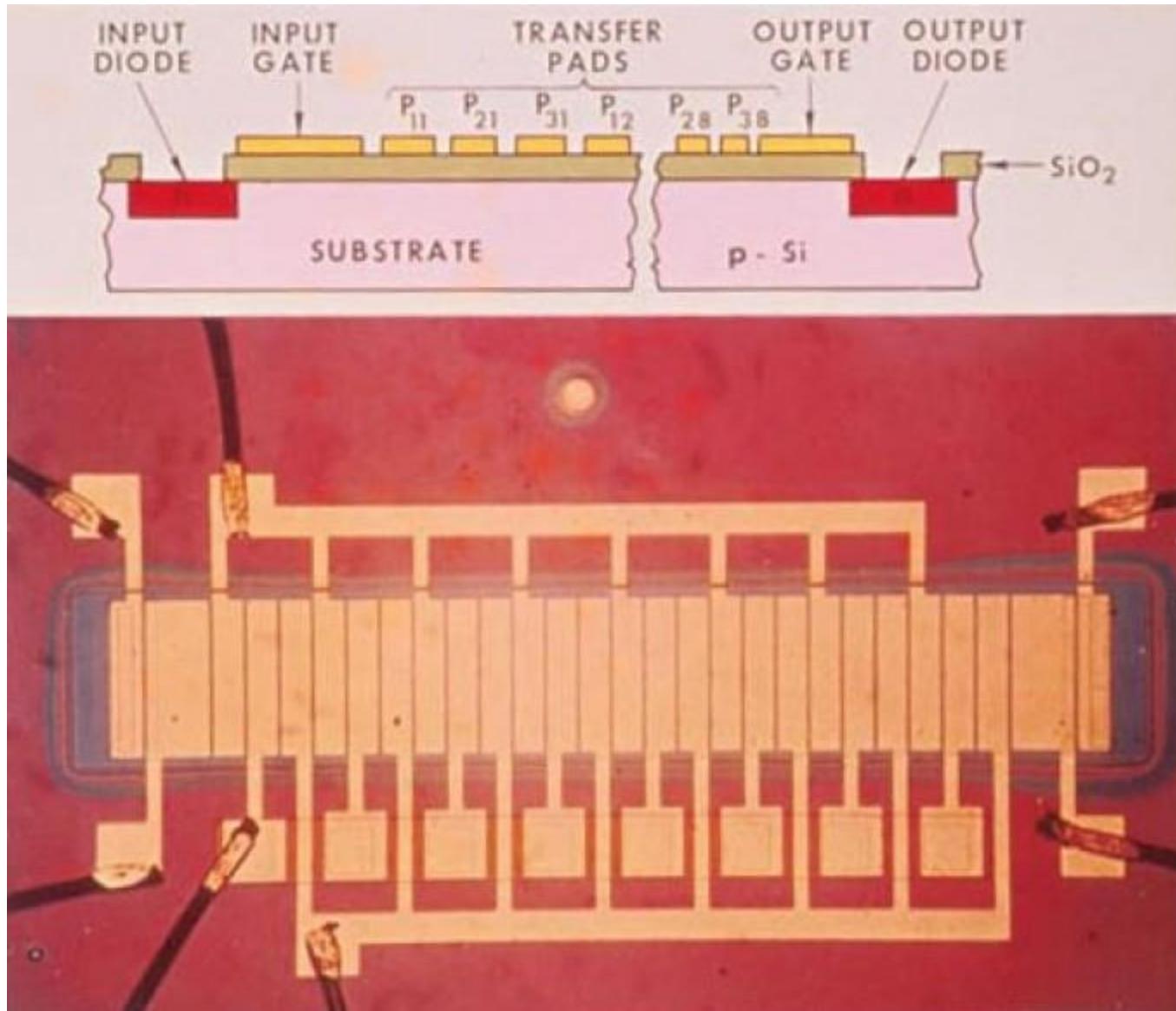
CCDs



Willard Boyle and George Smith at Bell Labs

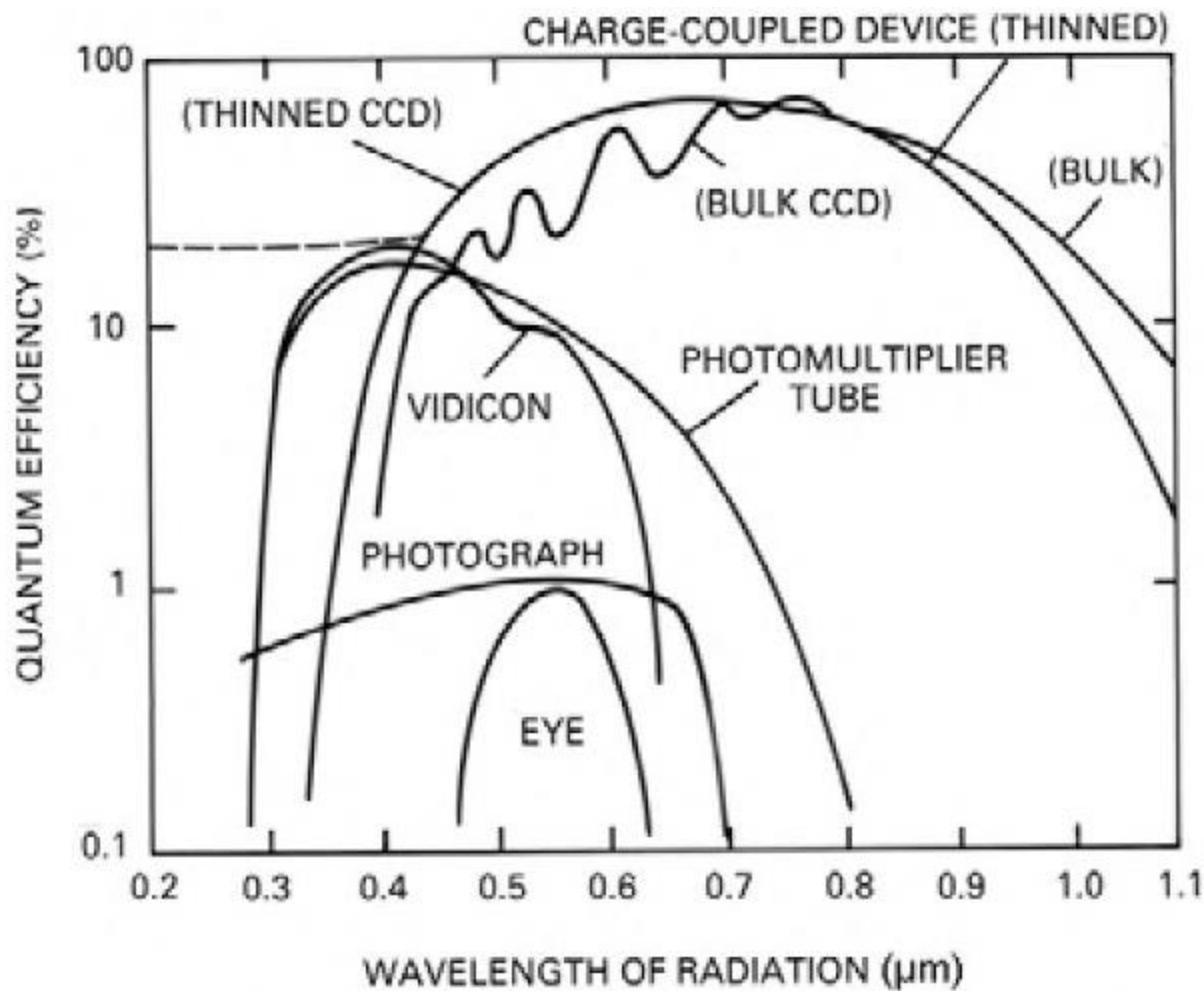
Charge coupling





Boyle & Smith, IEEE Spectrum, 1971

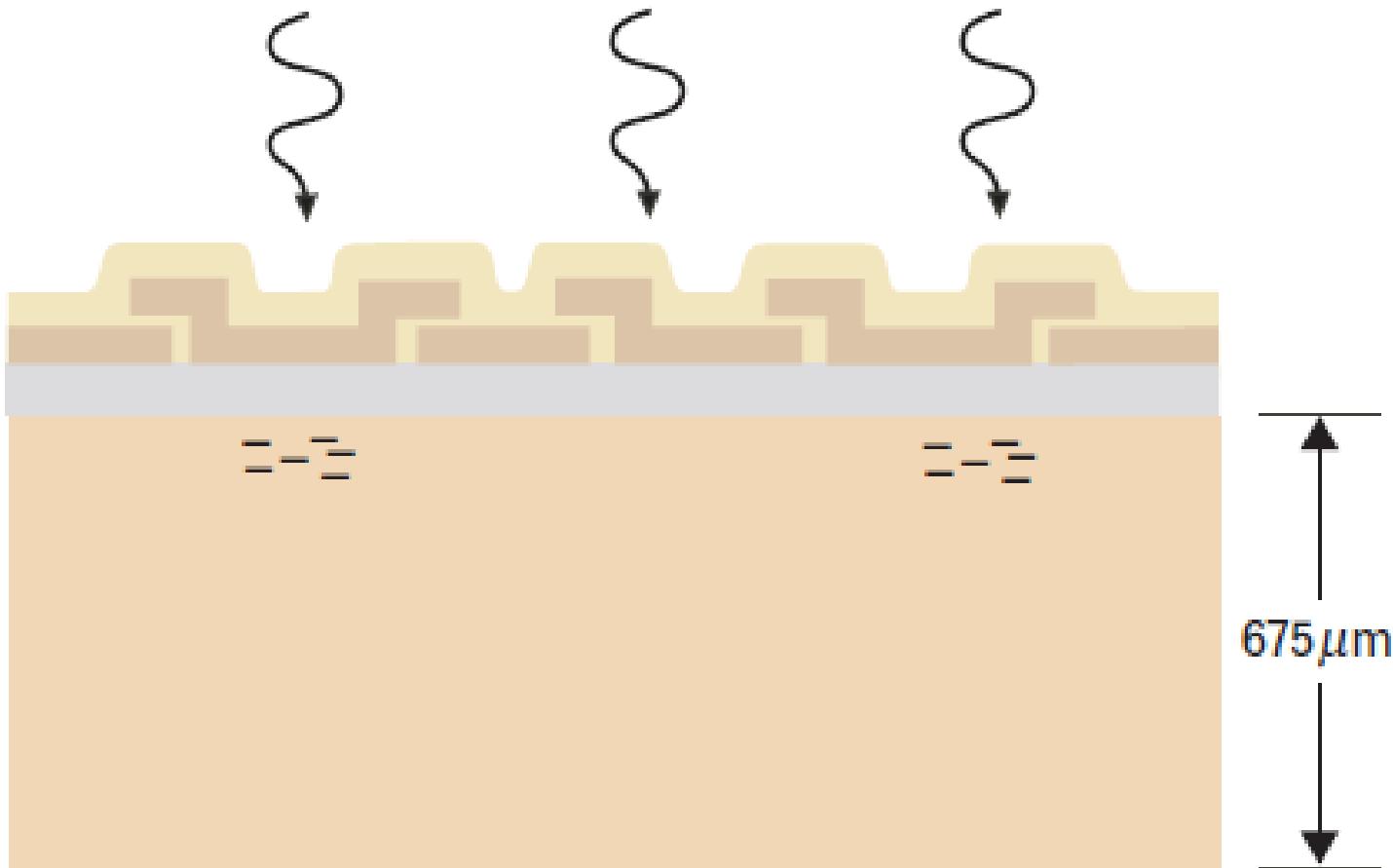
CCD sensitivity



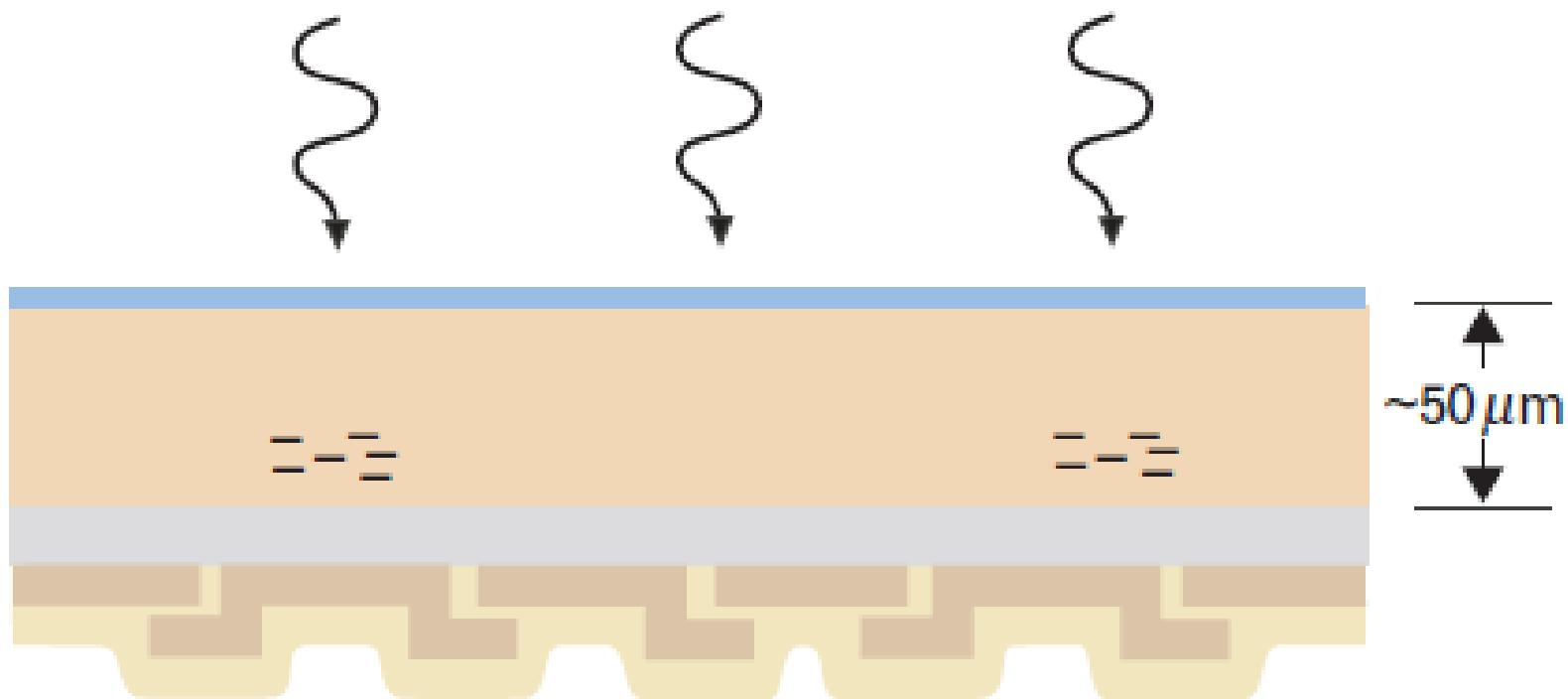
CCD operation

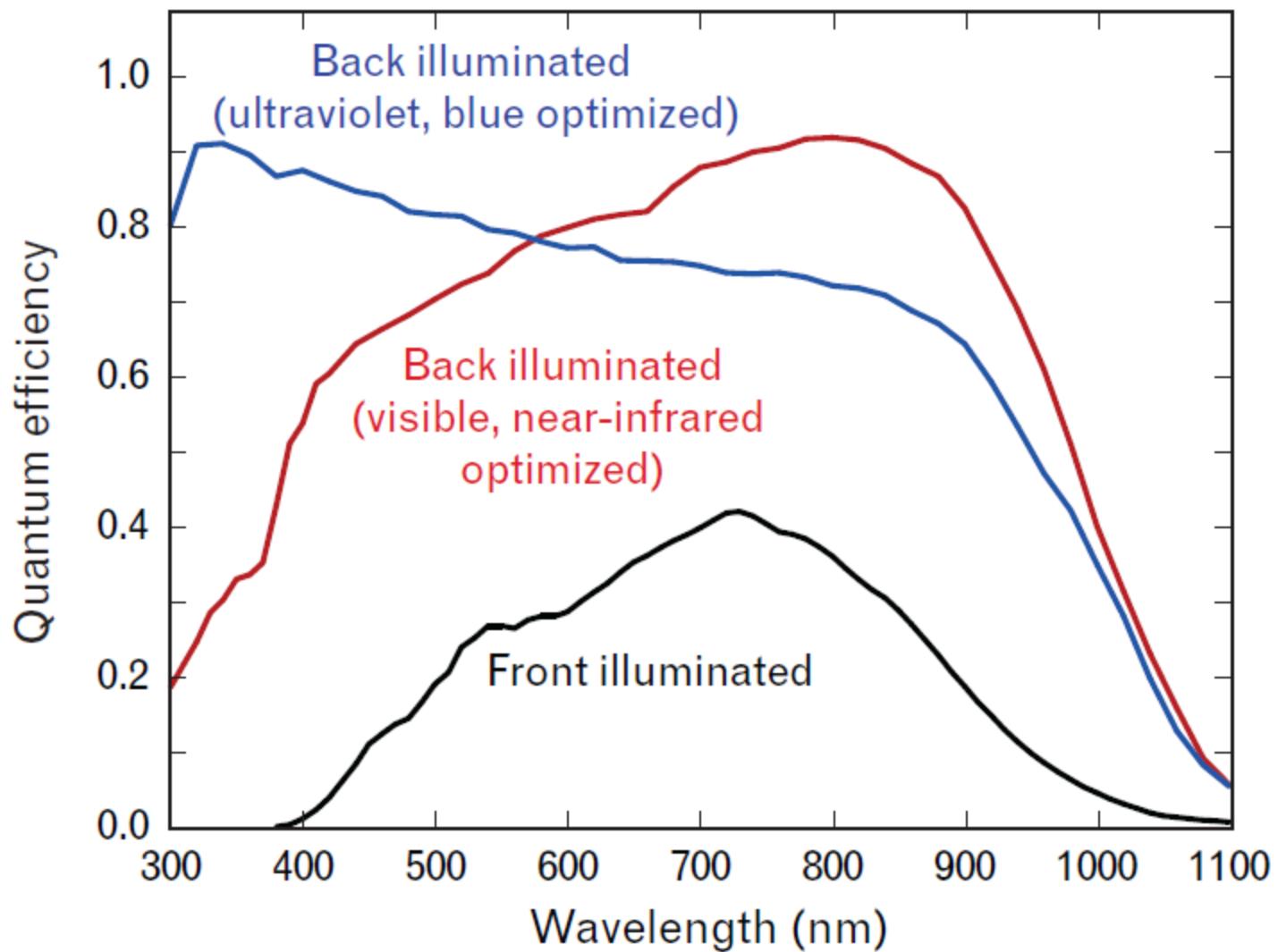
- Charge detection
- Charge collection
- Charge transfer
- Charge measurement
- Signal processing

Charge detection

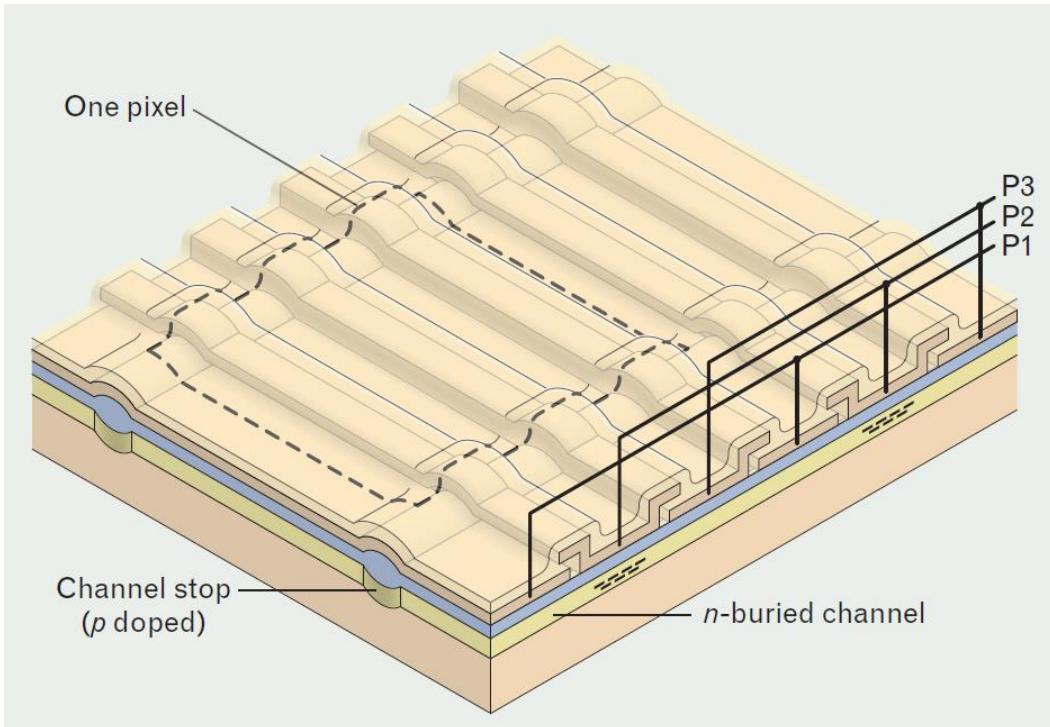


Backside illumination

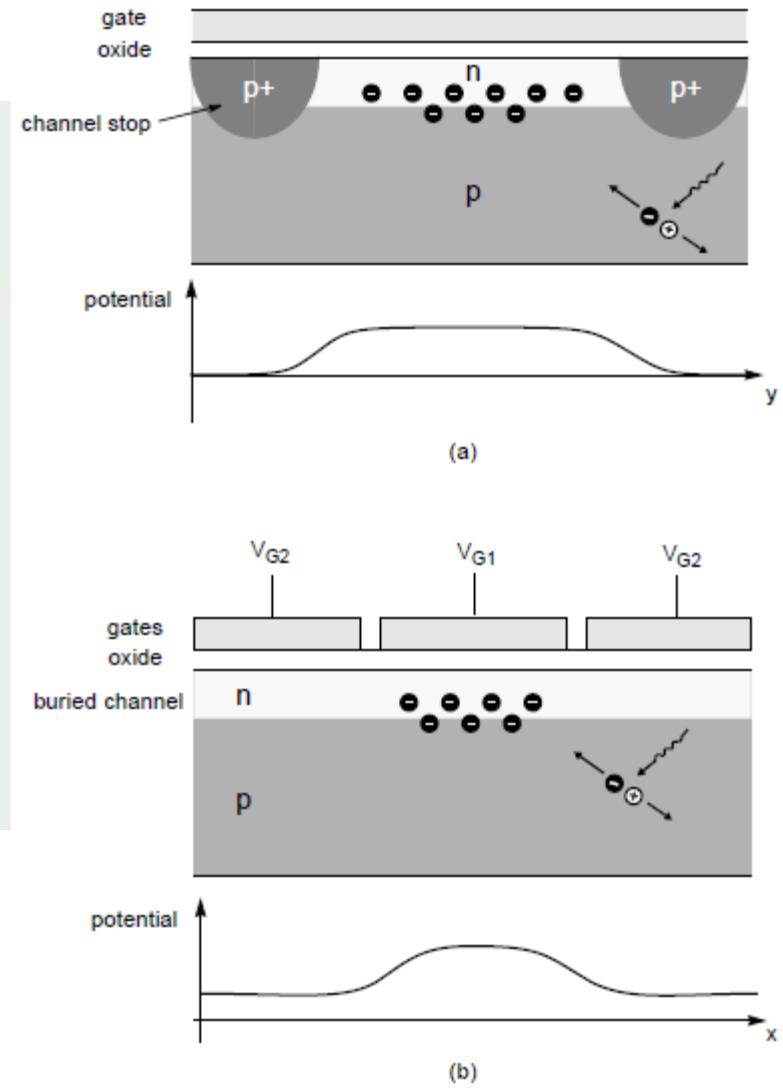




Charge collection

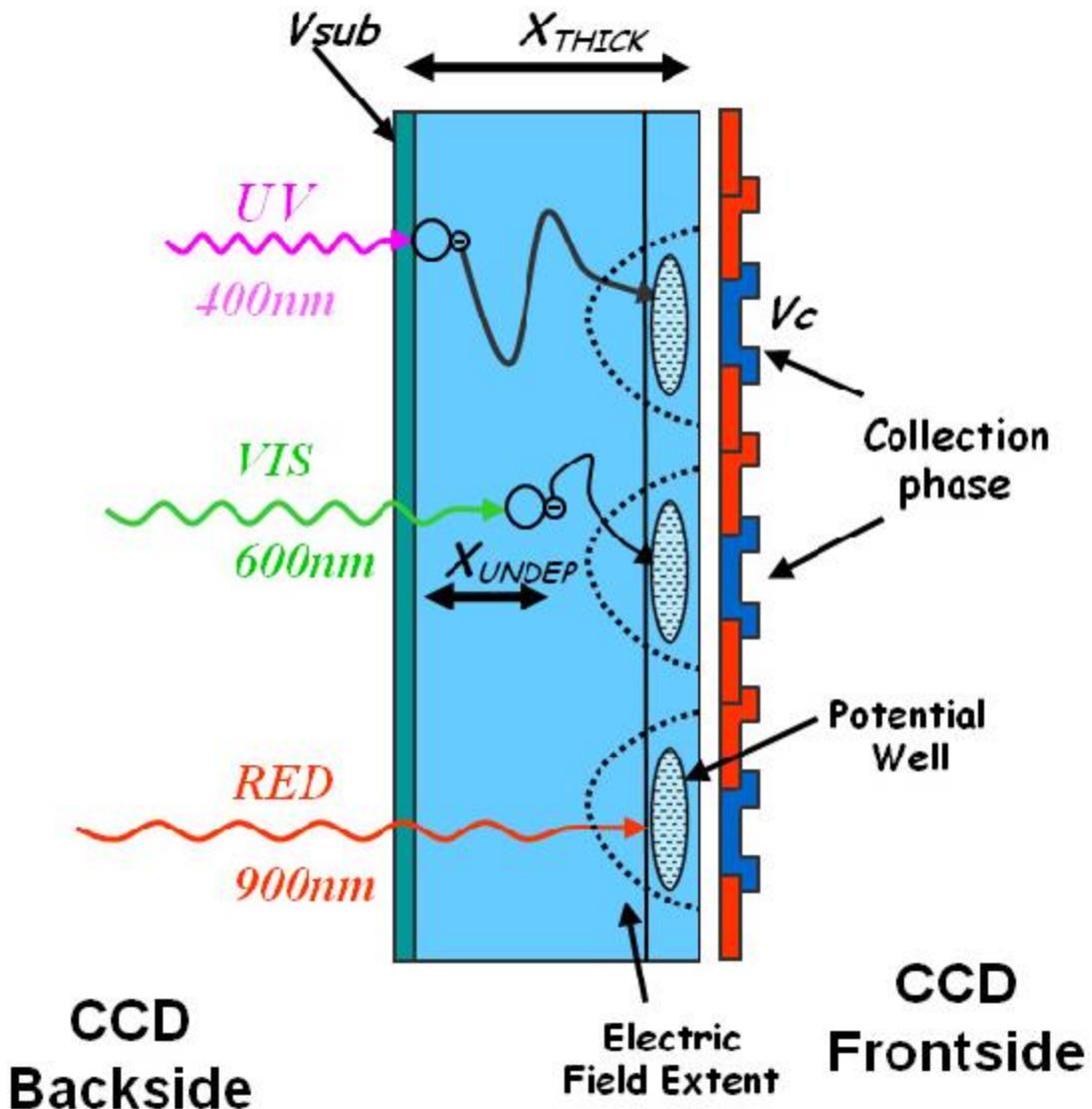


Burke et al, Lincoln Laboratory Journal, 2007

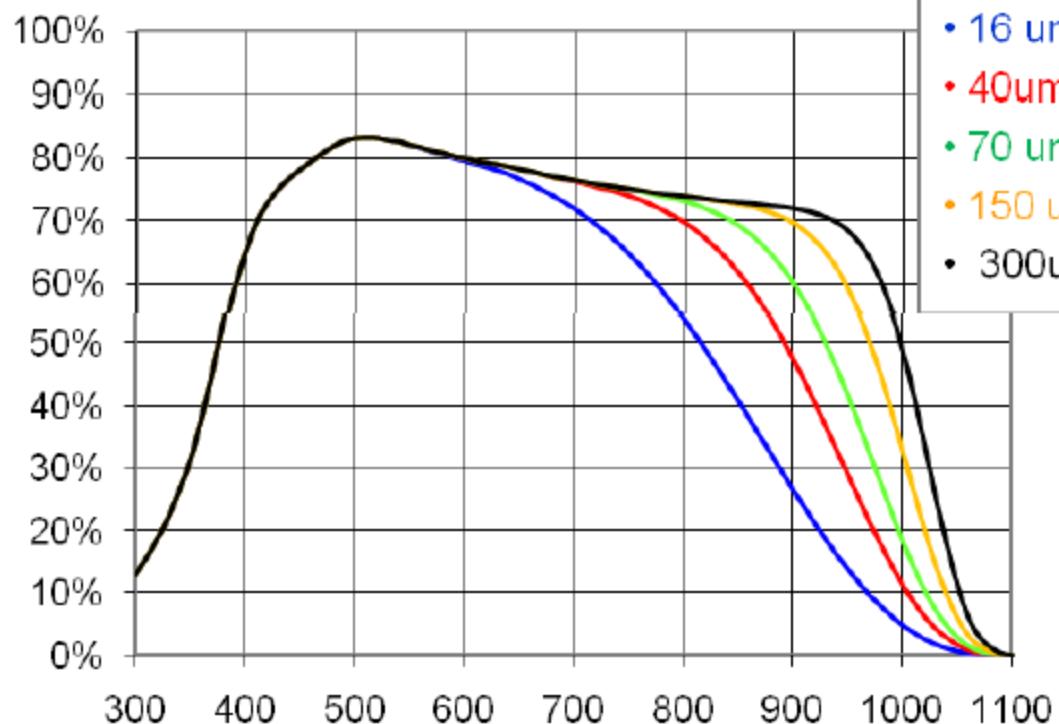


Blooming





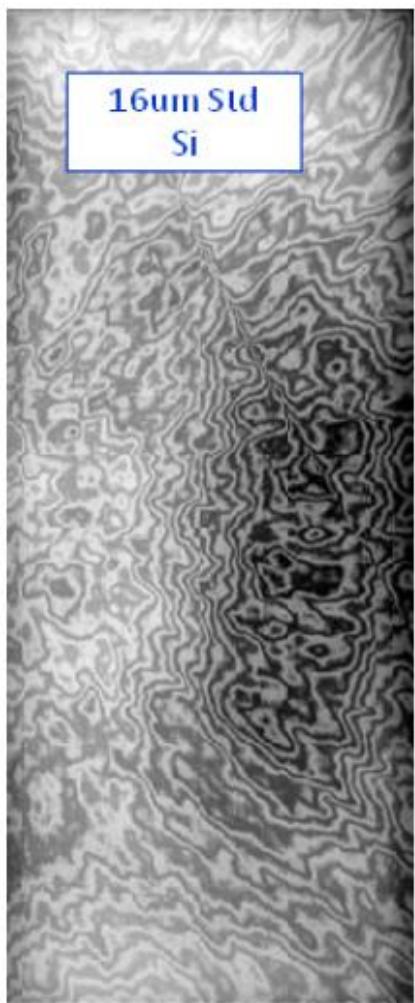
QE: -100°C Basic Broadband response



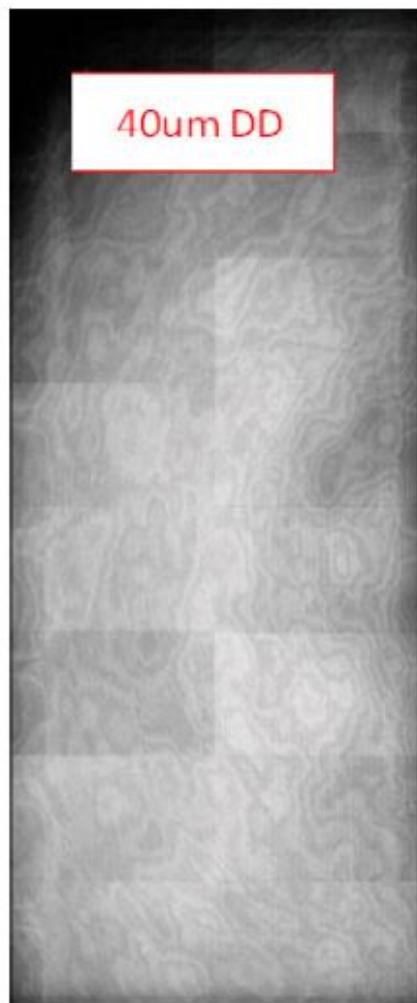
- 16 um standard silicon - 100 ohm-cm.
- 40um **deep depletion** - 1500 ohm-cm.
- 70 um bulk silicon - 3000 ohm-cm.
- 150 um high-rho - 3000 ohm-cm.
- 300um high-rho - 3000 ohm-cm.

Fringing

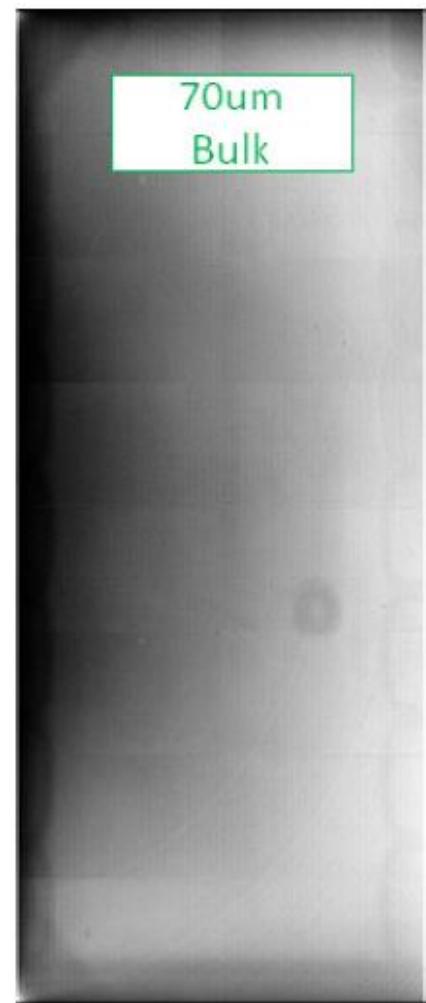
a)



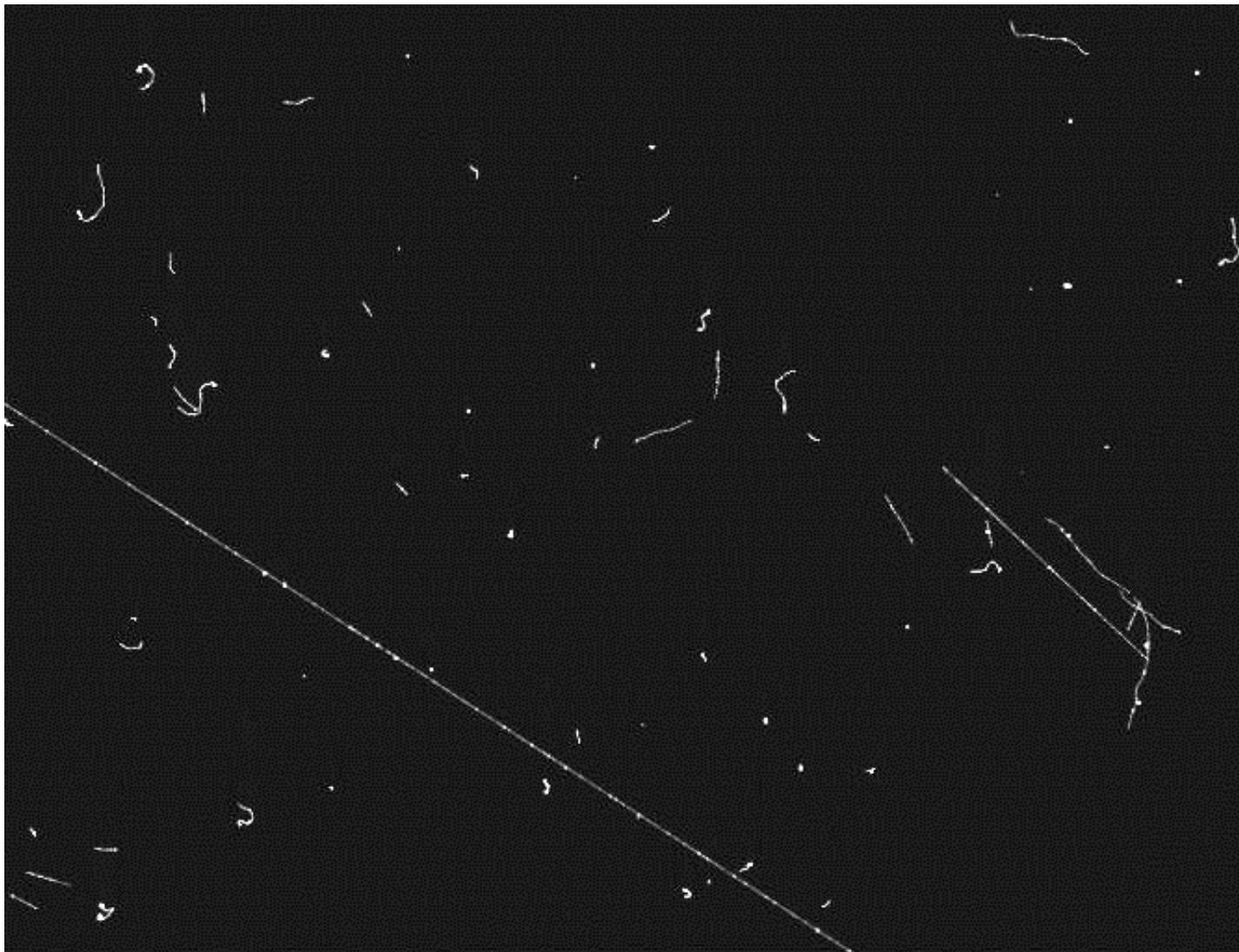
b)



c)

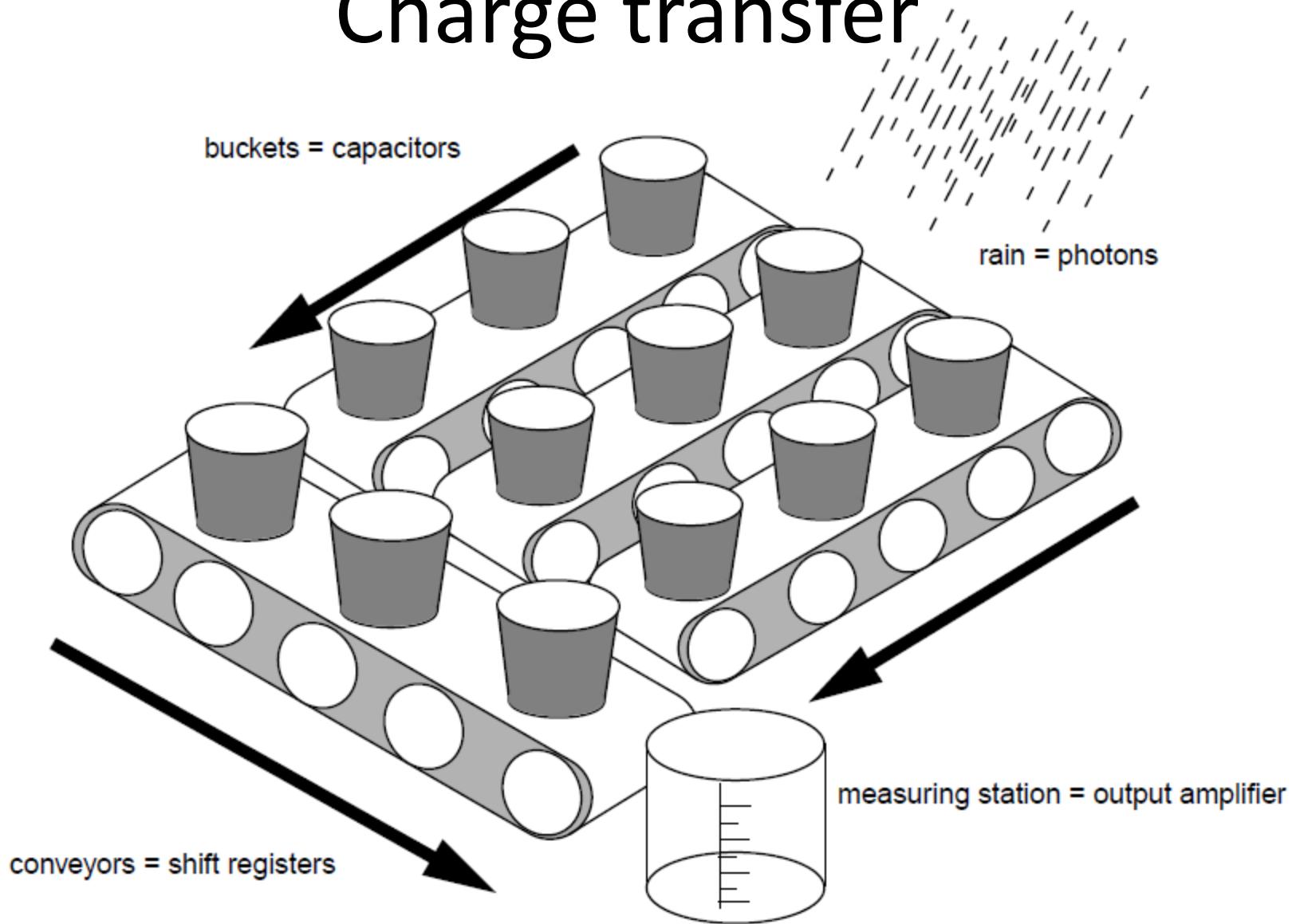


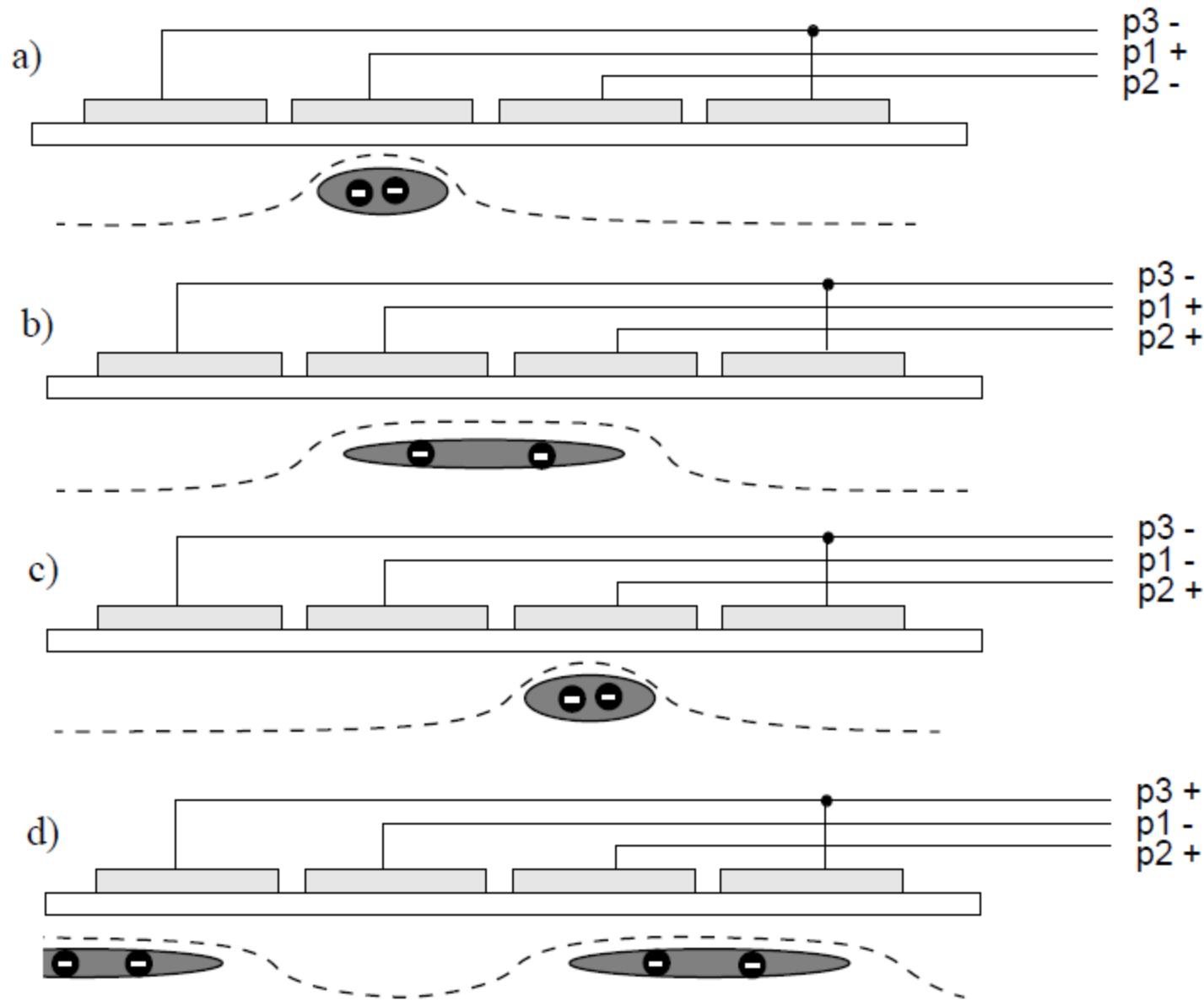
Cosmic rays

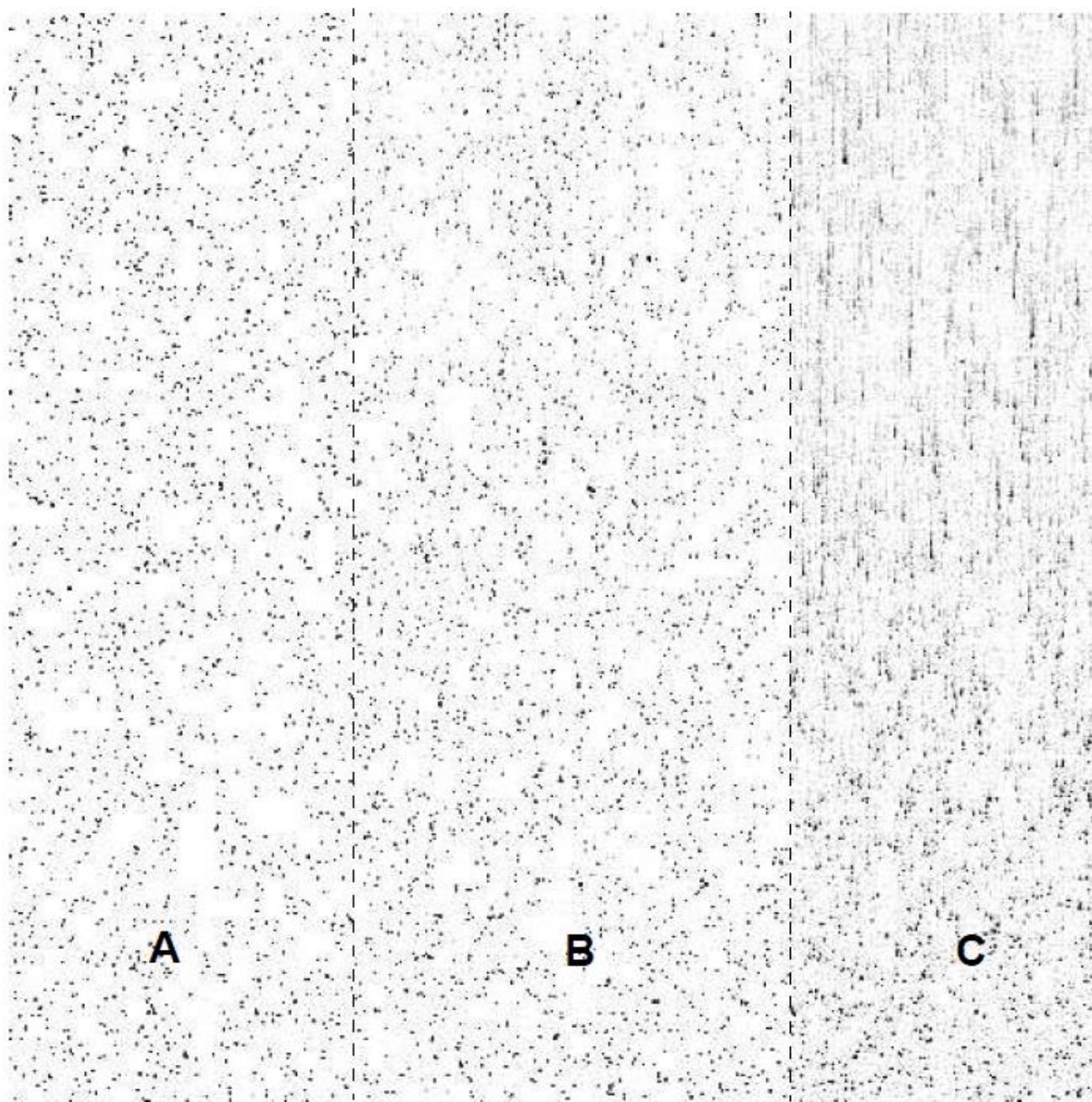


20 minute dark exposure with Hamamatsu fully-depleted CCD

Charge transfer

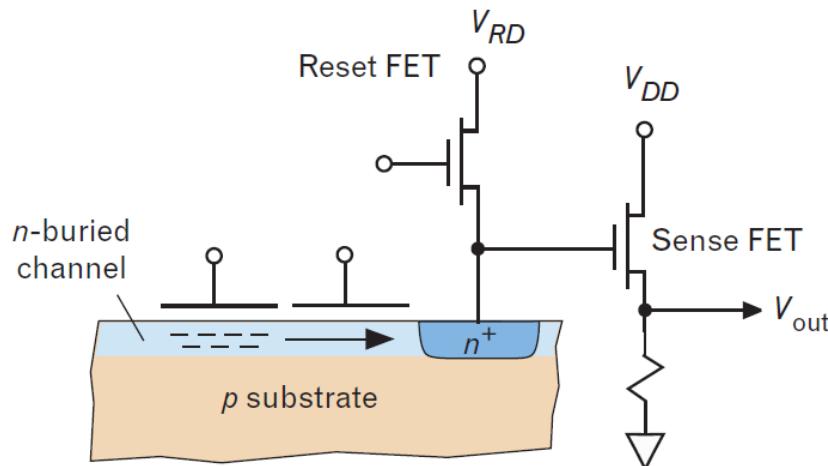






Radiation damaged CCD showing CTE problems

Charge measurement



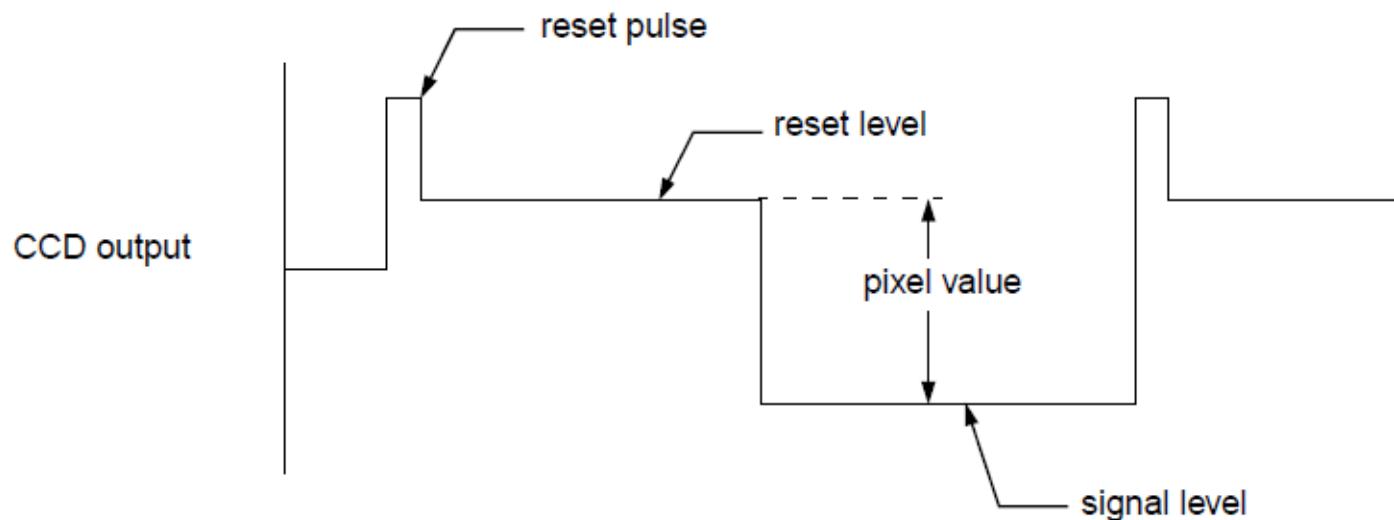
$$V_{out} = A(q/C_s)$$

A = gain of transistor

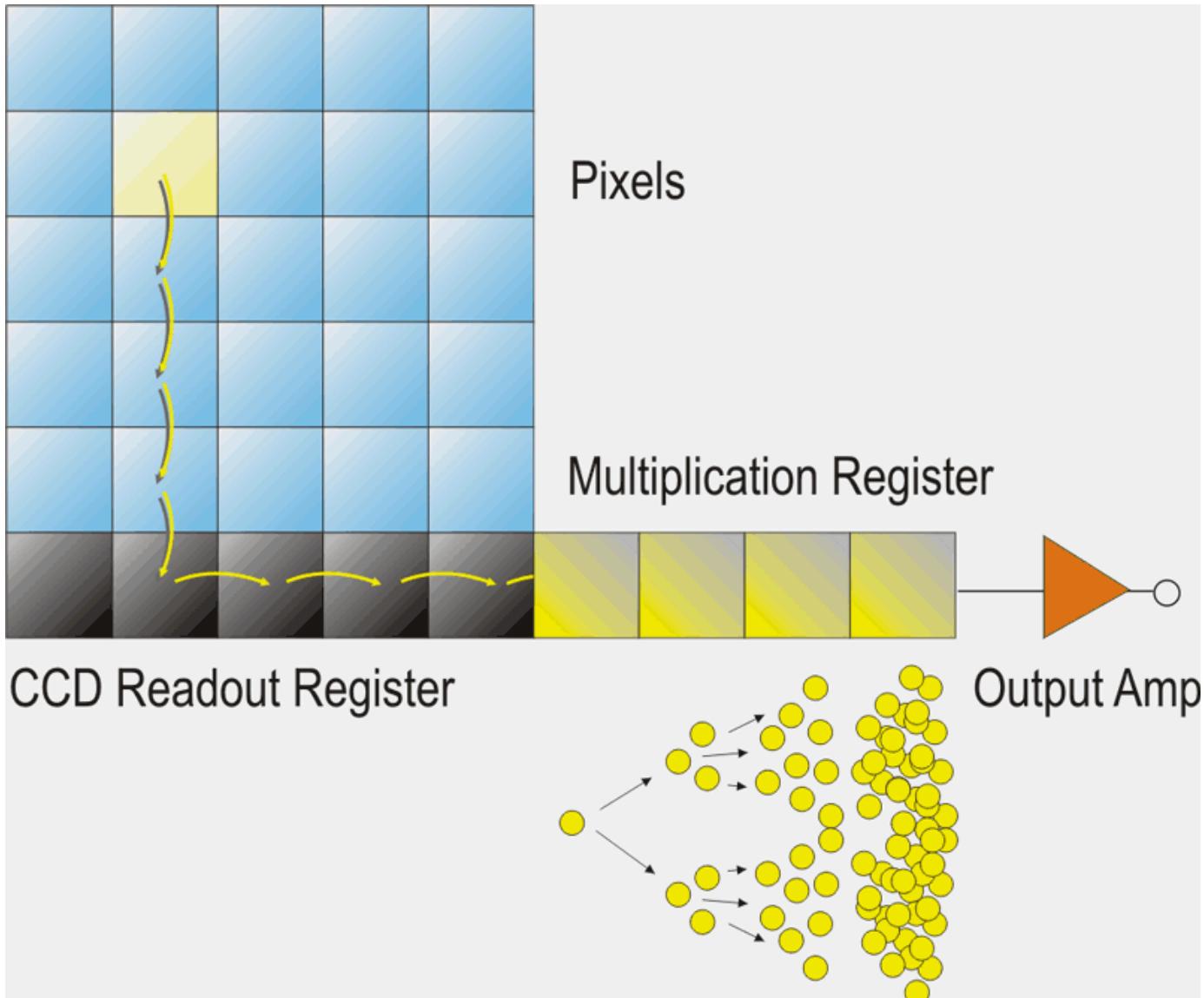
q = charge

C_s = capacitance of sense node

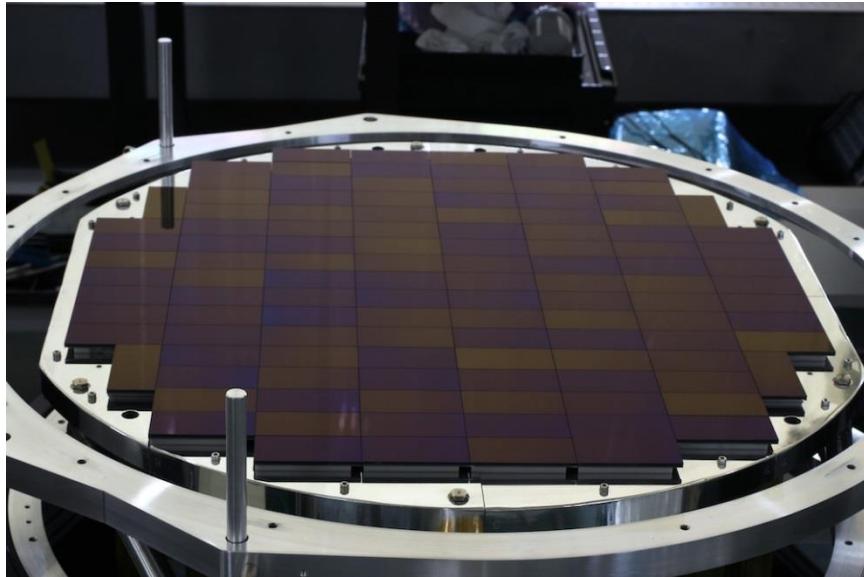
Burke et al, Lincoln Laboratory Journal, 2007



Electron-multiplying (EMCCD)



Large mosaics

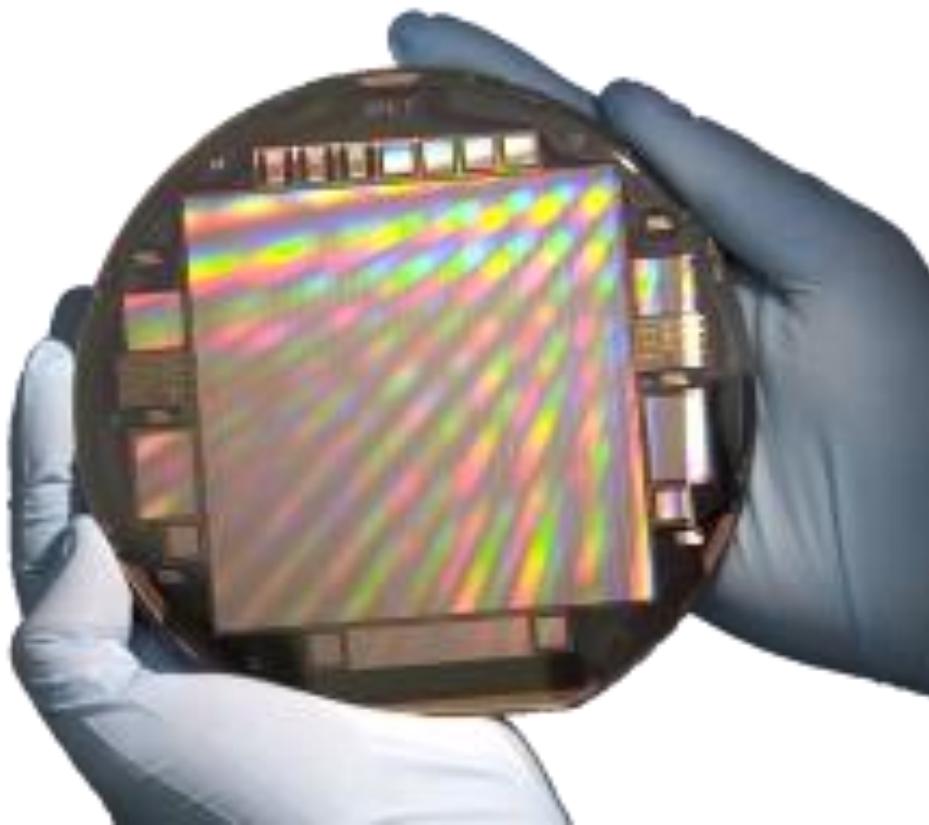


HyperSuprimeCam
116 CCDs
60cm focal plane



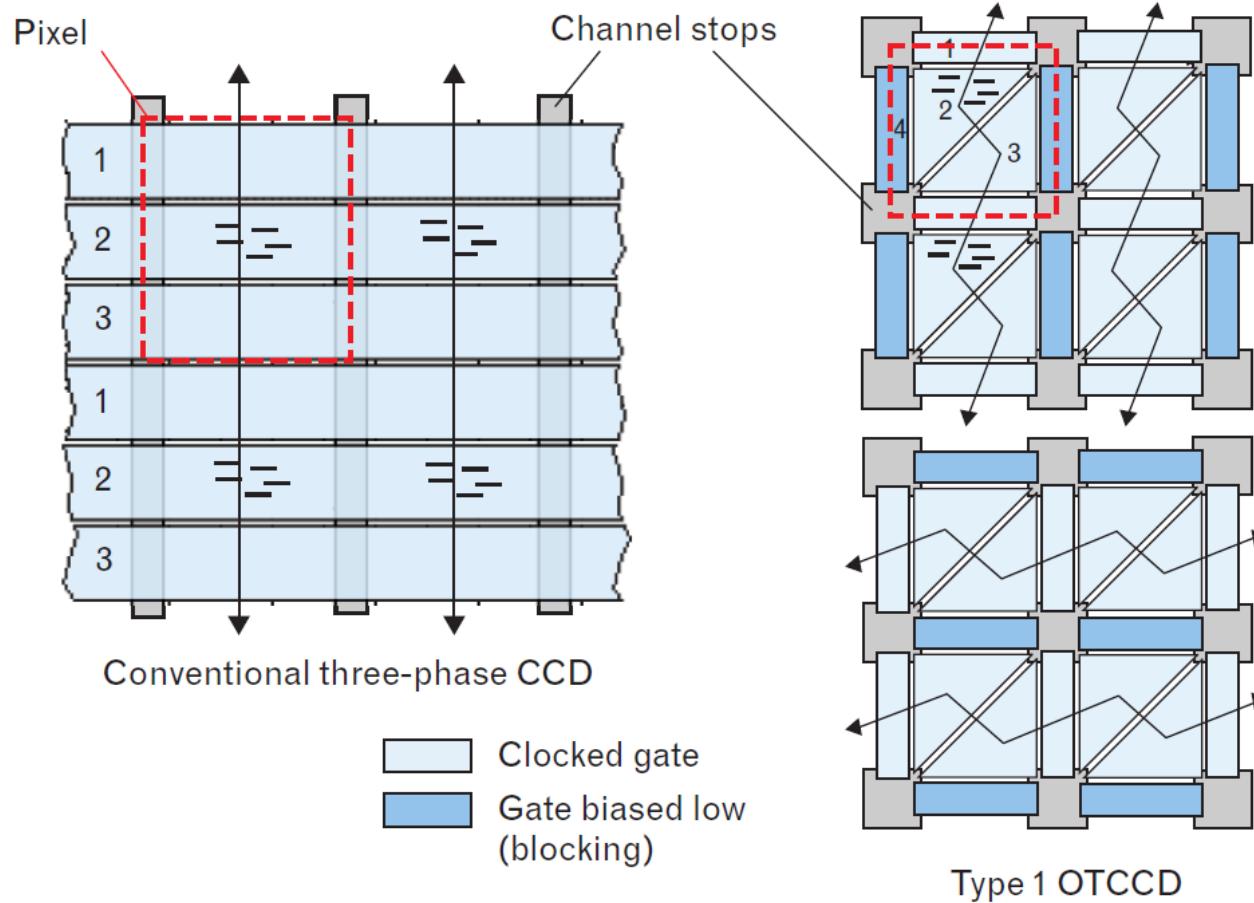
LSST
201 CCDs
64cm focal plane
3.2 GPixels

Large format CCDs

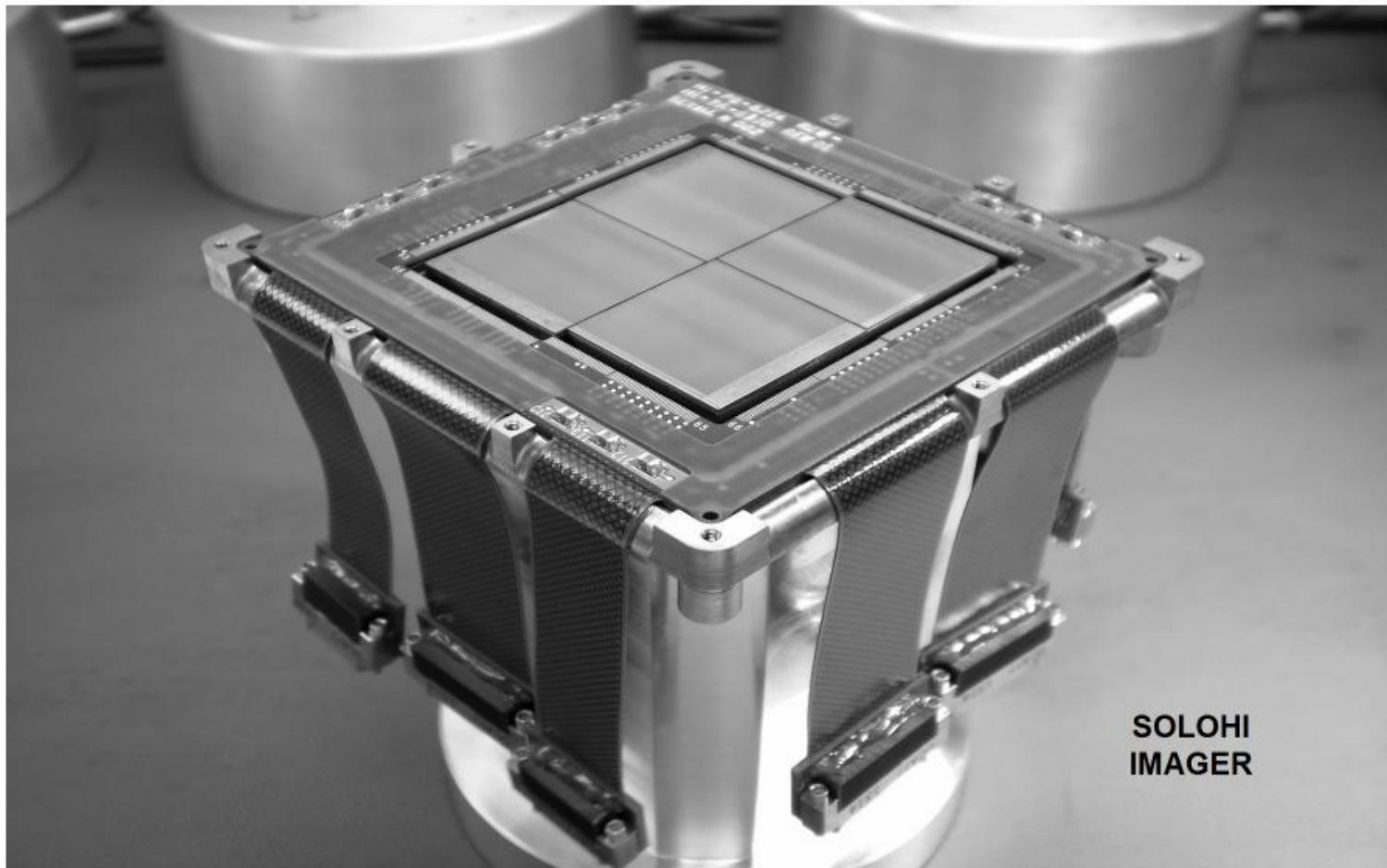


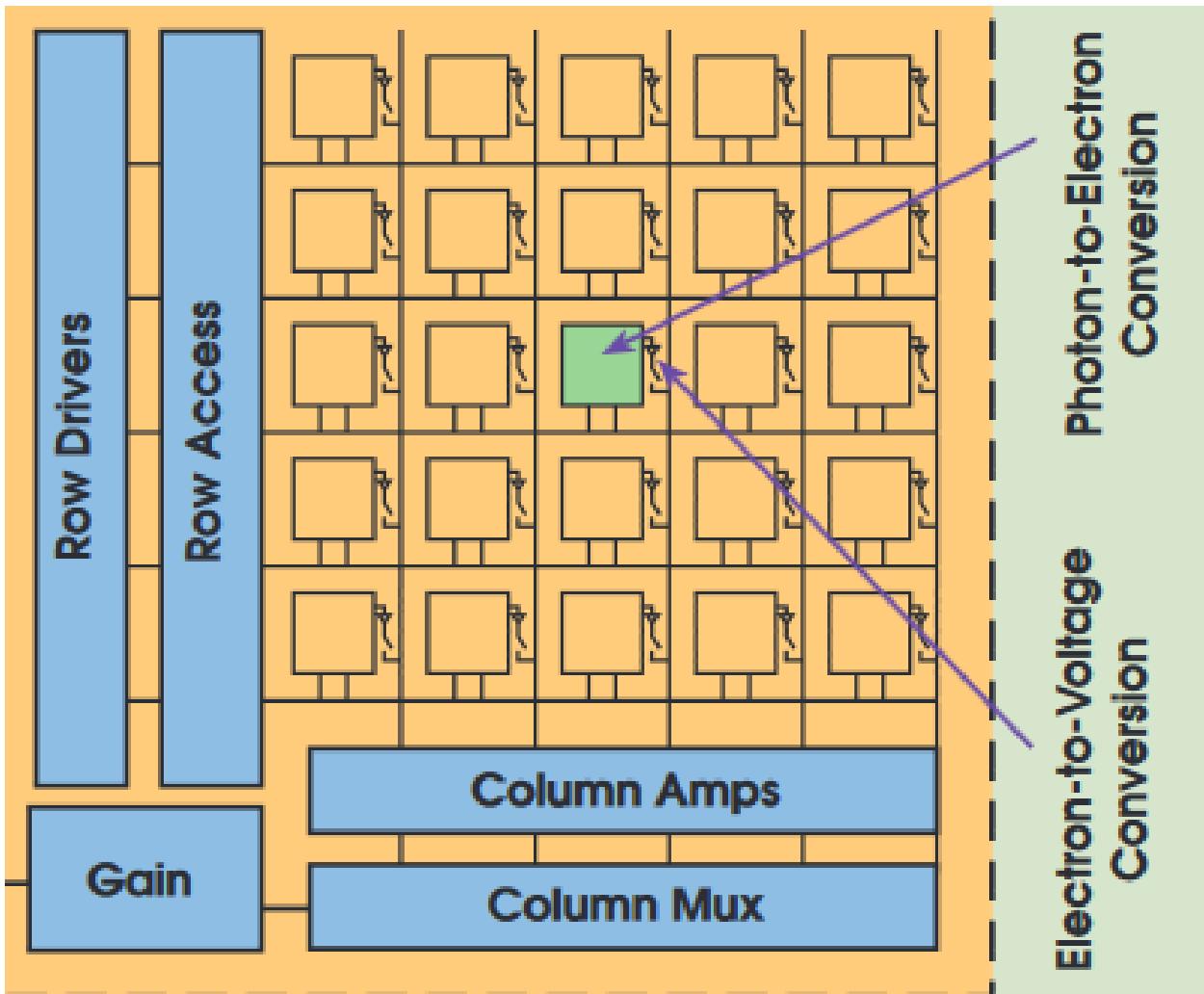
Semiconductor Technology Associates
10kx10k pixels
125mm wafer

Orthogonal transfer CCD



CMOS imagers





Anatomy of the Active Pixel Sensor Photodiode

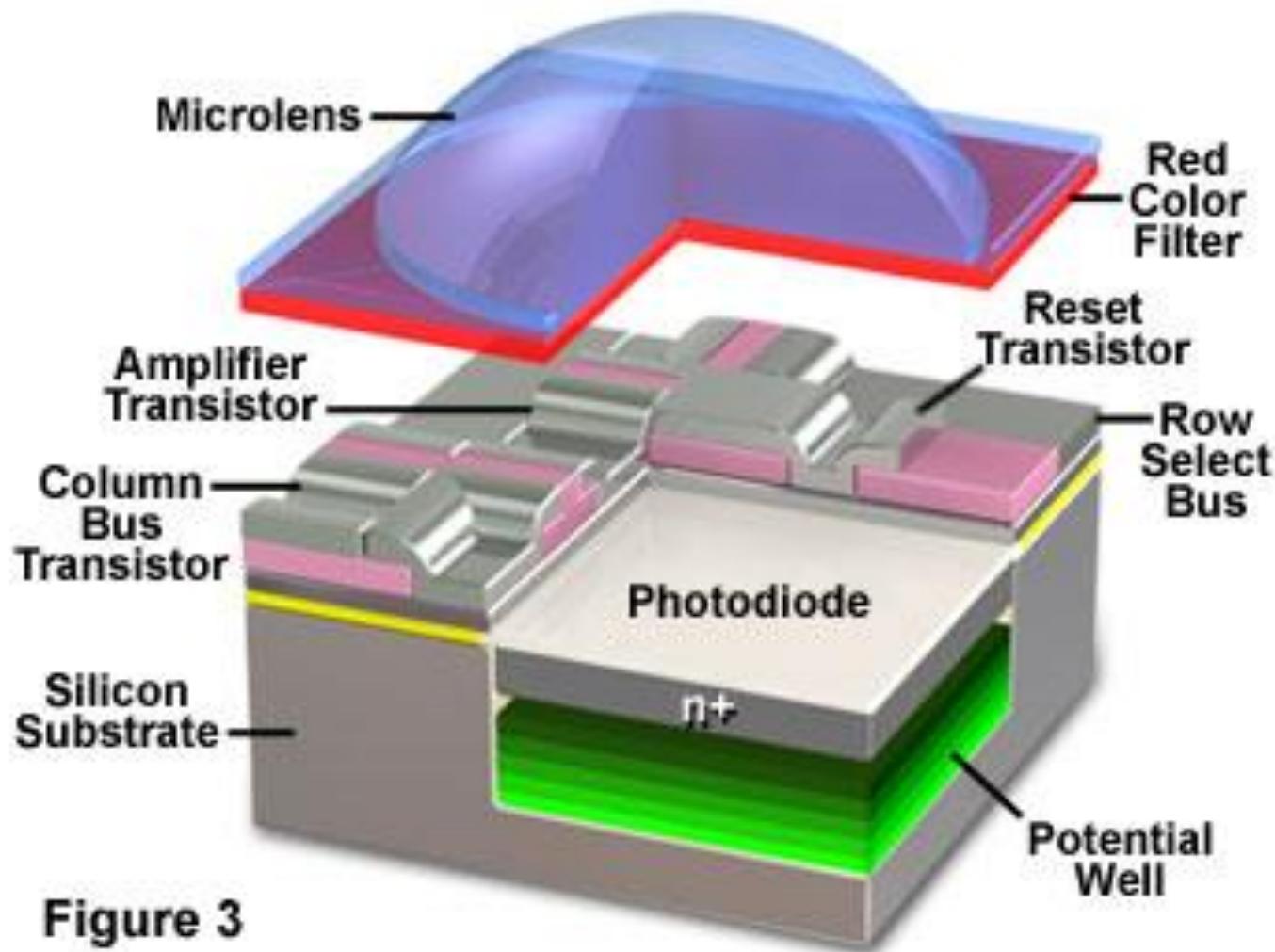
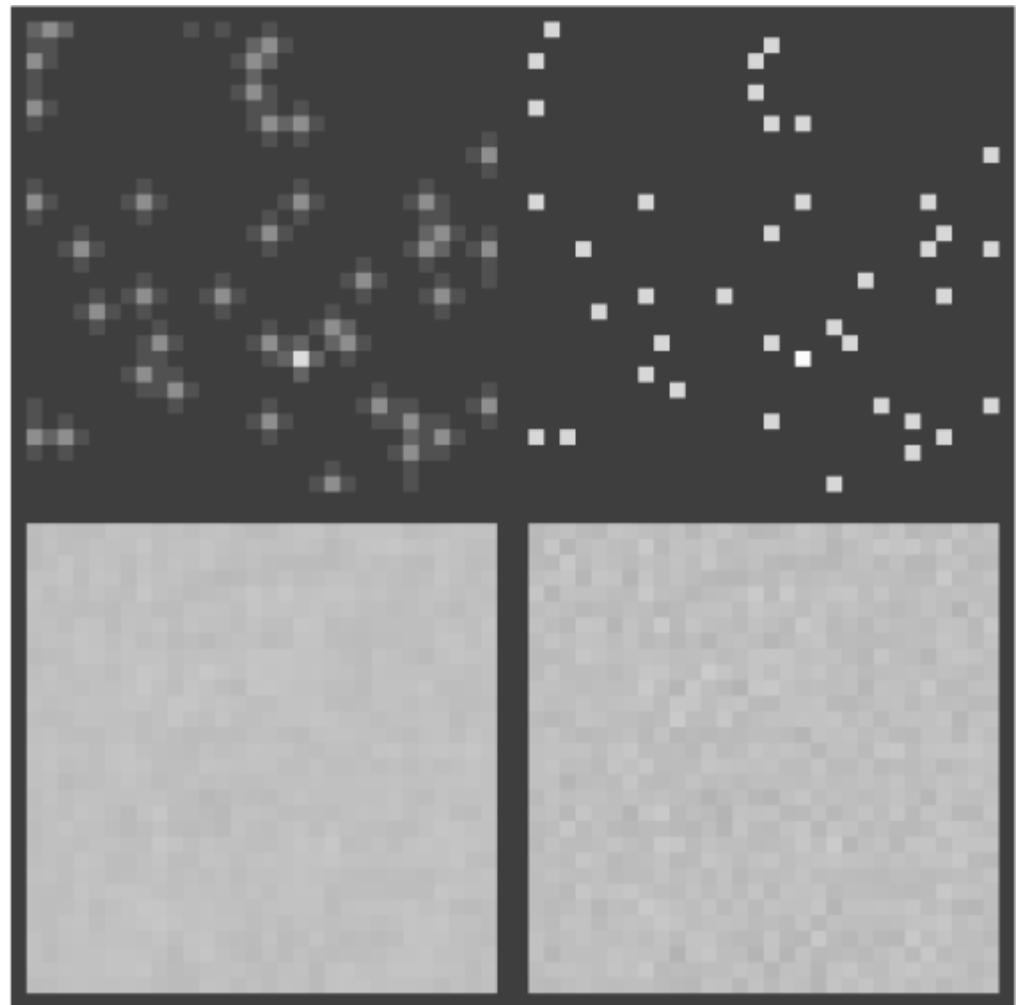
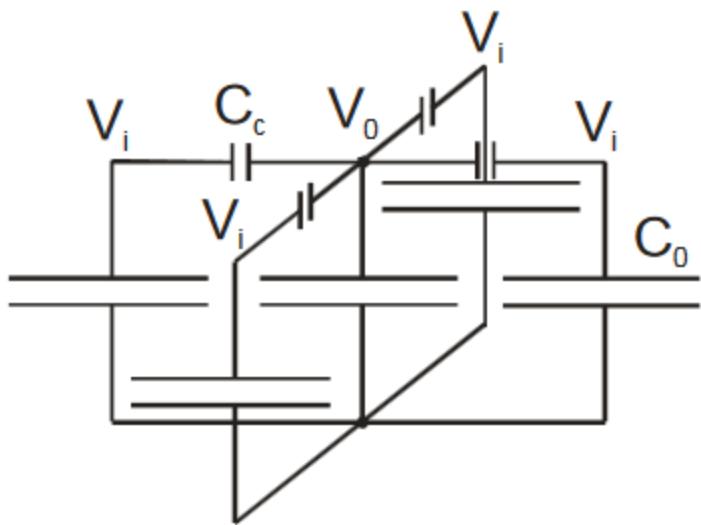


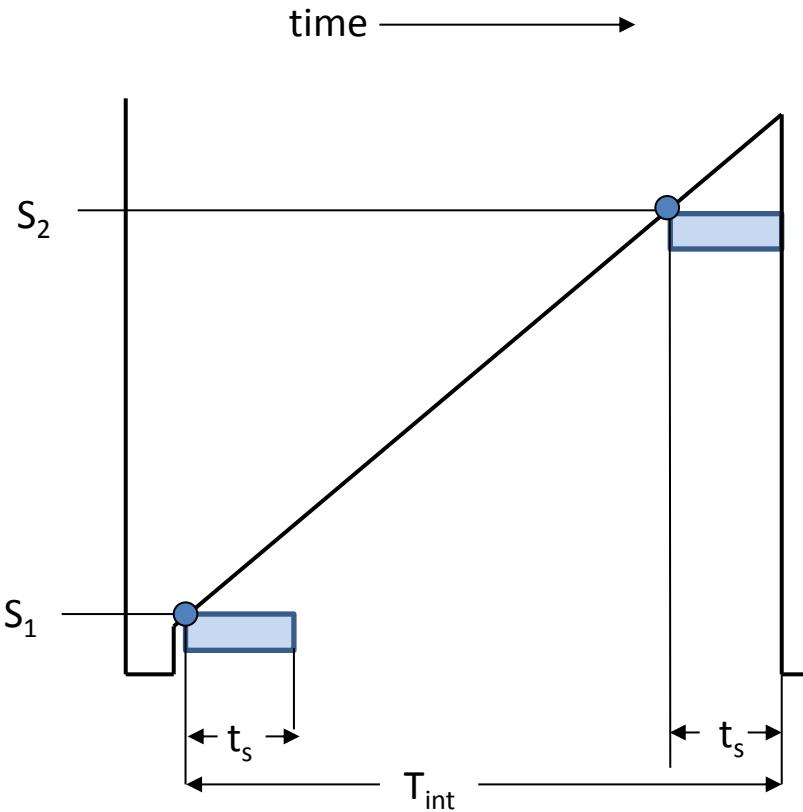
Figure 3

Inter-Pixel Capacitance (IPC)



Finger et al. 2005

Correlated double sampling



$$\text{signal} = S_2 - S_1 = (T_{int} - t_s) \cdot F$$

F = flux (e/s)

T_{int} = total integration time

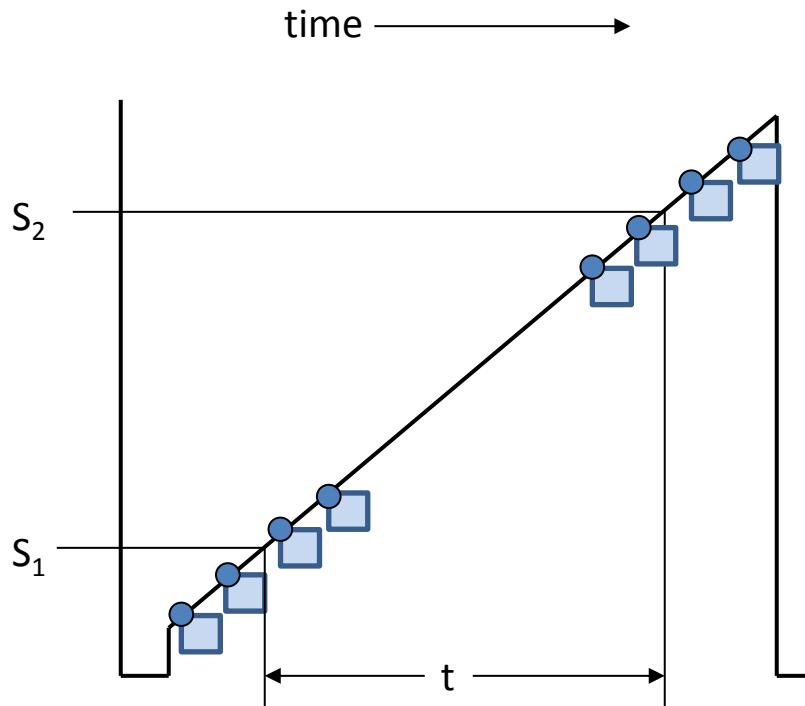
t_s = sample time

$$t_s = \frac{\text{pixels}}{\text{outputs} \times \text{pixel rate}}$$

$$\text{noise} = \sqrt{2\sigma^2}$$

σ = read noise (e)

Fowler sampling



$$\text{signal} = S_2 - S_1 = (T_{int} - nt_s) \cdot F$$

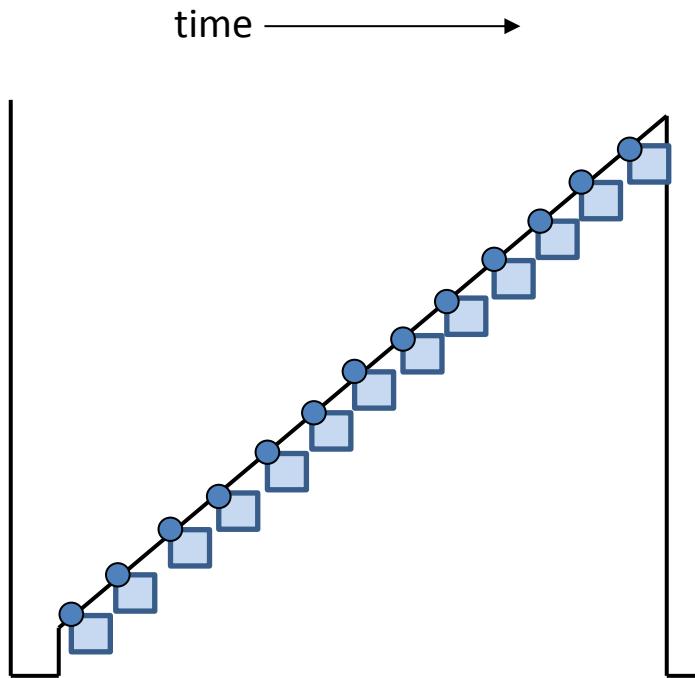
F = flux (e/s)

n = number of samples (4)

$$\text{noise} = \sqrt{\frac{2\sigma^2}{n}}$$

σ = read noise (e)

Up-The-Ramp sampling



signal = F

F = flux (e/s)

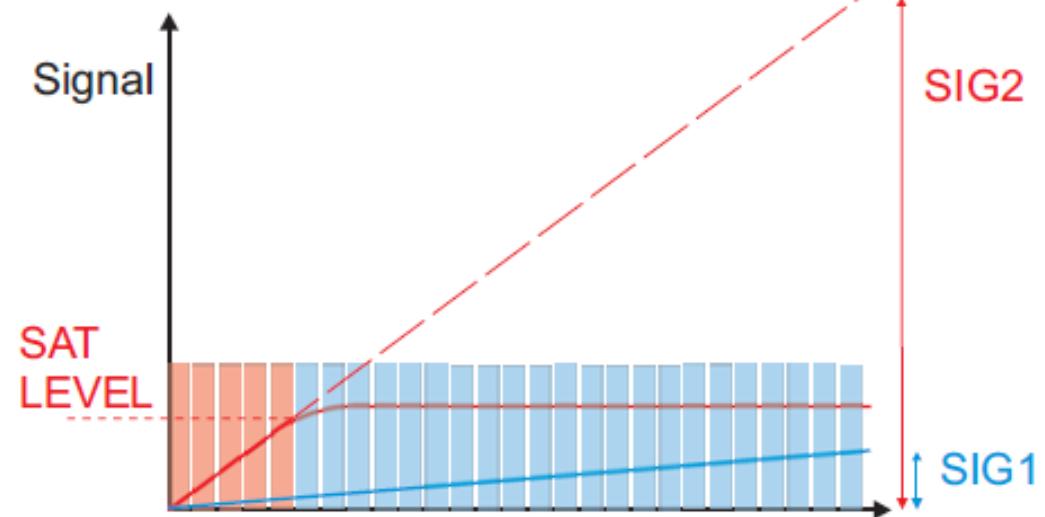
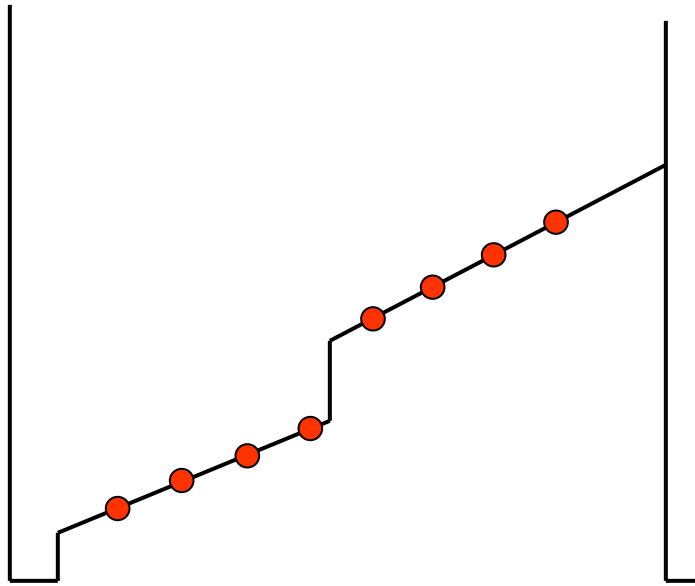
$$\text{noise} = \sqrt{\frac{12N}{N^2-1} \cdot \frac{\sigma^2}{{T_{int}}^2}}$$

σ = read noise (e)

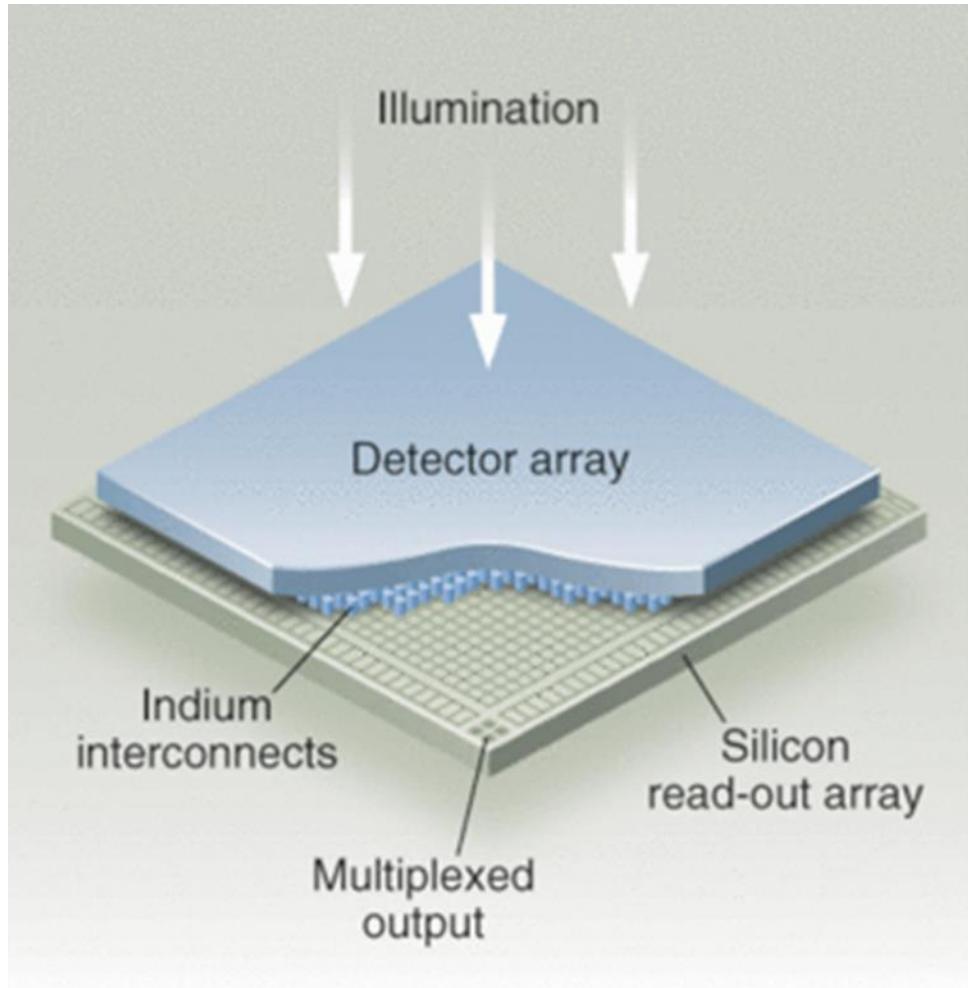
N = number of samples (13)

Cosmic rays/saturation

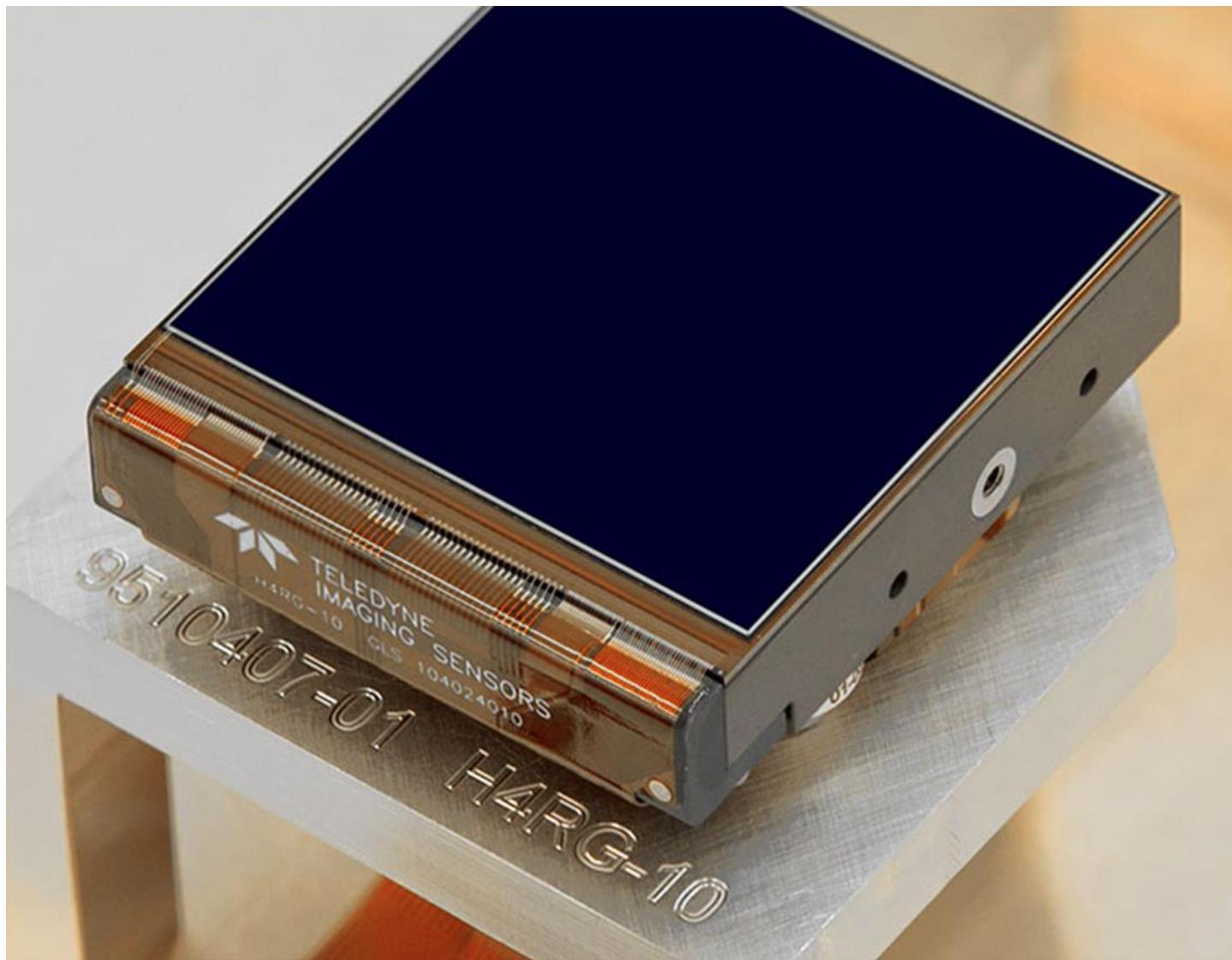
time →

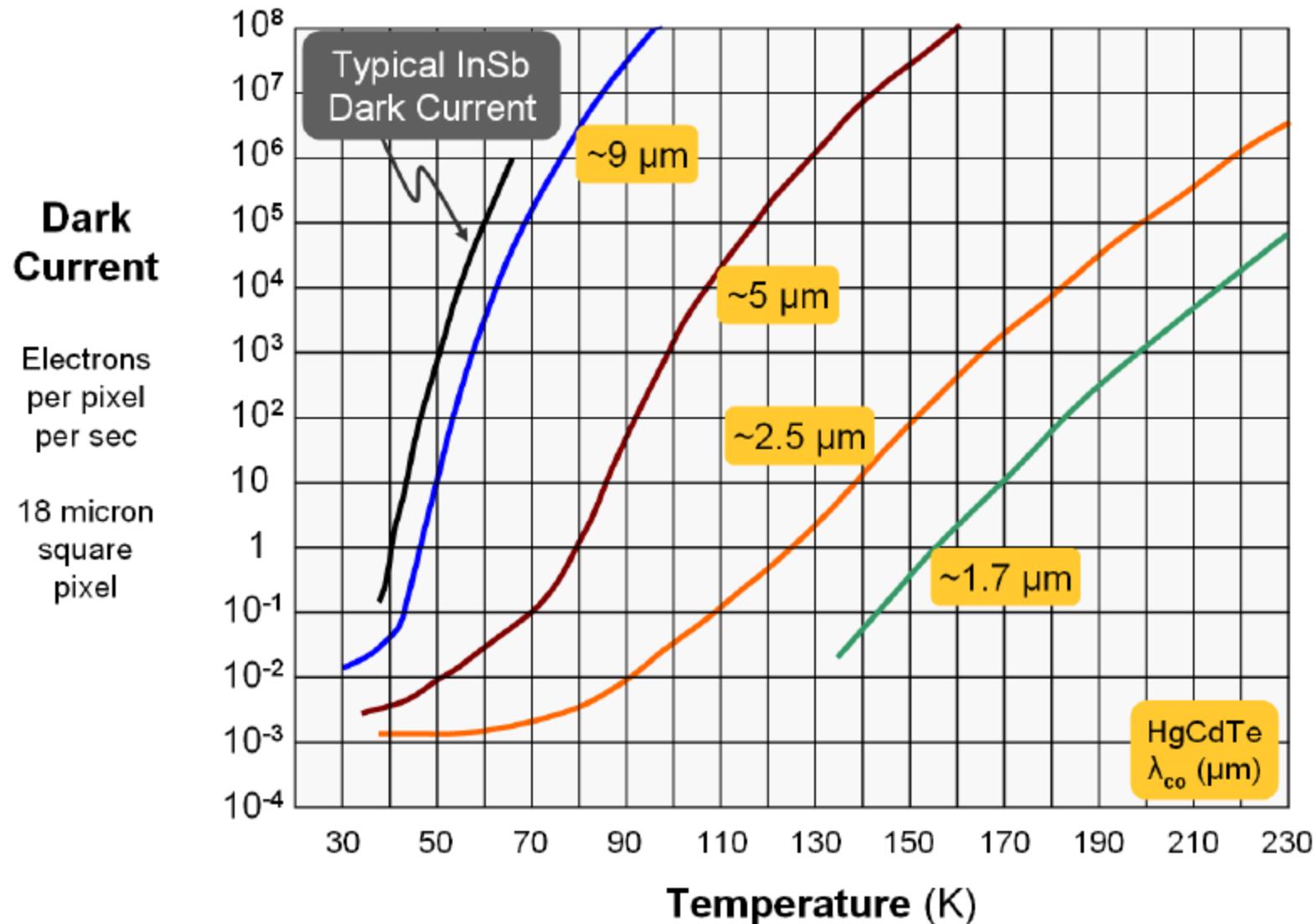


Hybrid CMOS

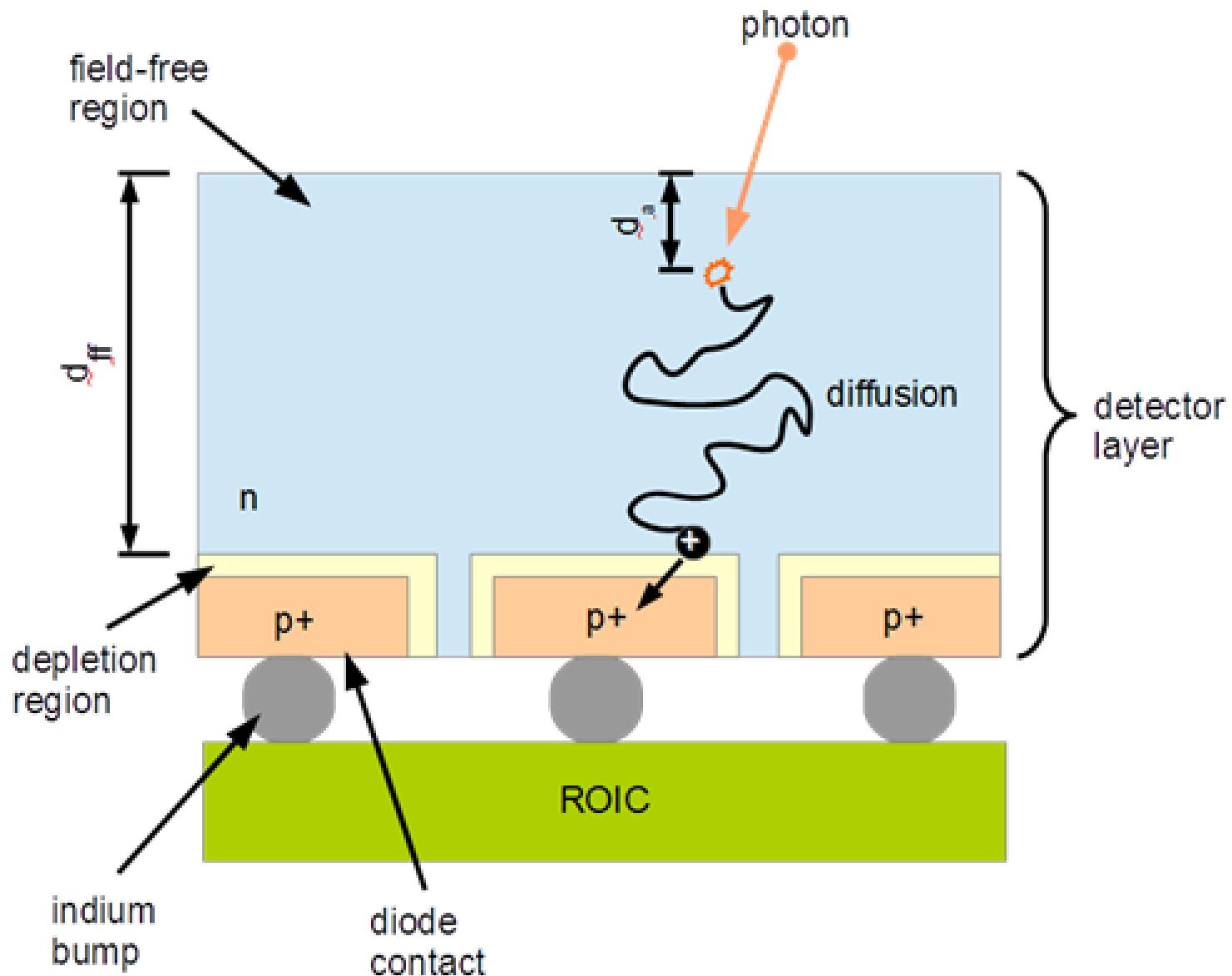


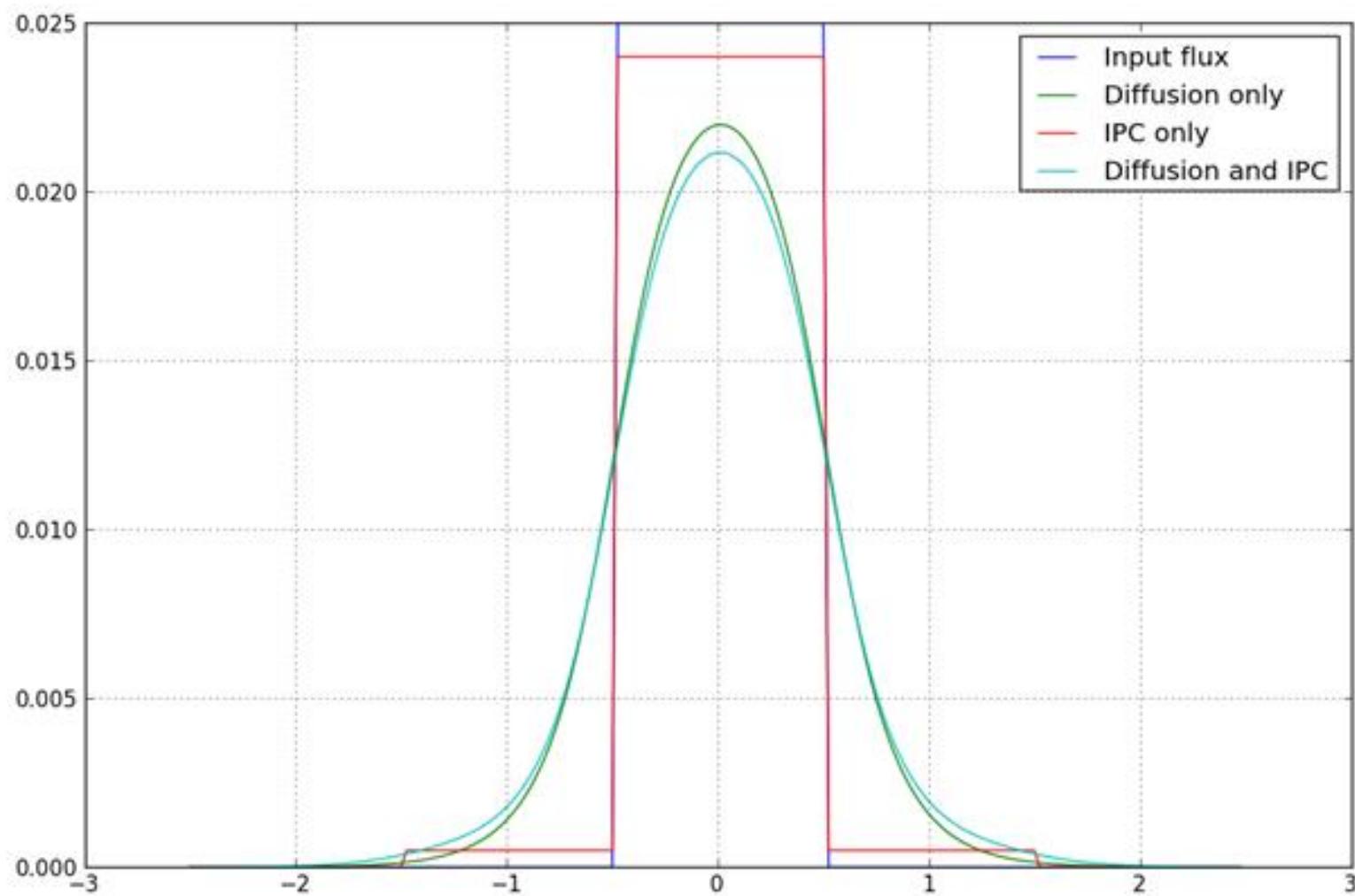
ReadOut Integrated Circuit (ROIC)
Multiplexer (mux)



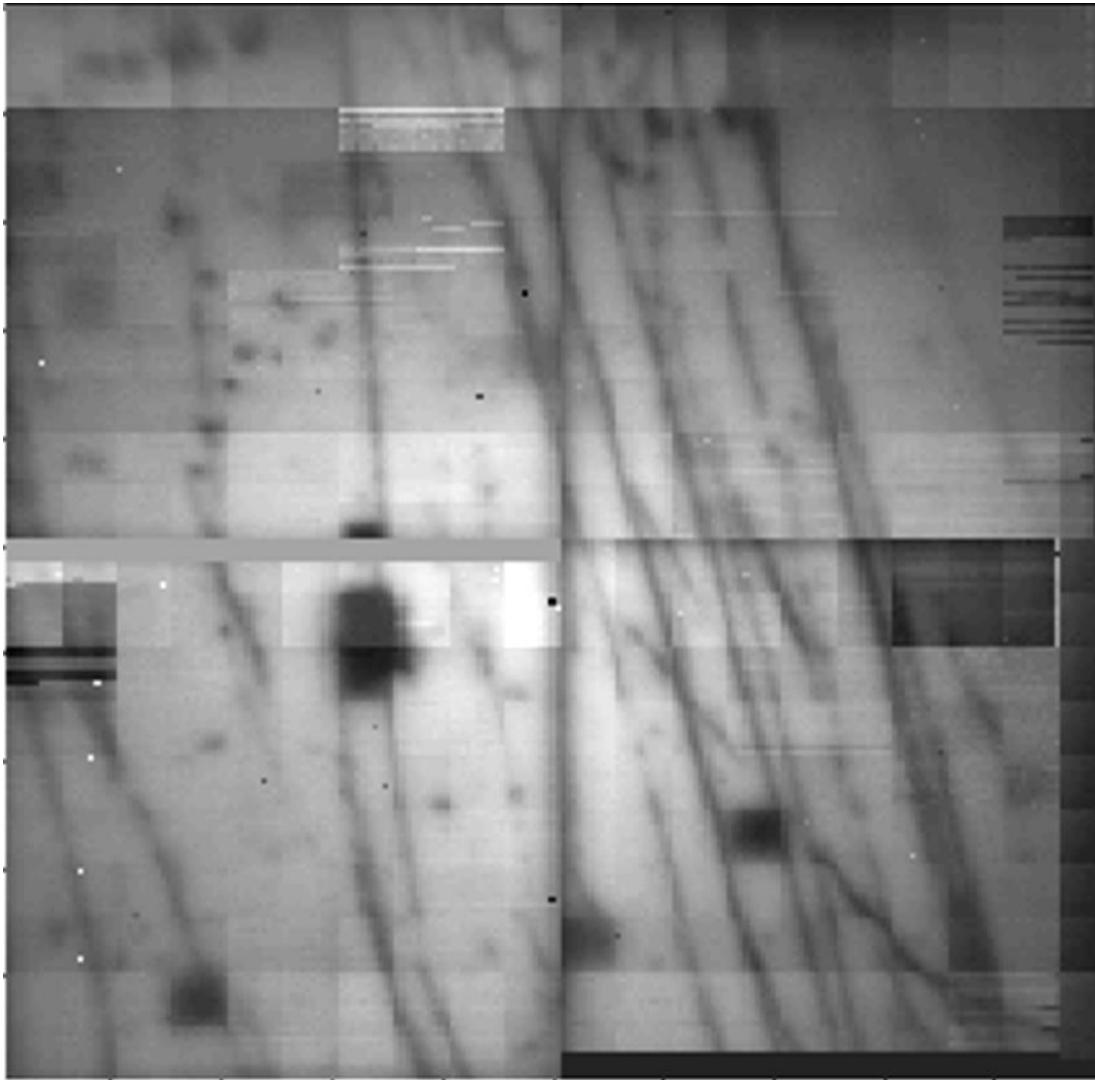


Diffusion





Sub-pixel scale defects



SAPHIRA IR APD

